





TCAN1473-Q1 SLLSFV9 – JULY 2024

TCAN1473-Q1 Automotive Signal Improvement Capable CAN FD Transceiver With Sleep Mode

1 Features

Texas

INSTRUMENTS

- AEC Q100 Qualified for automotive applications
- Functional Safety-Capable
- Implements Signal Improvement Capability (SIC) as defined in ISO 11898-2:2024
 - Actively improves bus signal by eliminating ringing and enhancing bit symmetry
- Wide input operational voltage range
- V_{IO} level shifting supports: 1.7V to 5.5V
- Operating modes:
 - Normal mode
 - Silent mode
 - Standby mode
 - Low-power sleep mode
- High-voltage INH output for system power control
- Local wake-up support via the WAKE pin
- · Defined behavior when unpowered
 - Bus and IO terminals are high impedance (no load to operating bus or application)
- Protection features:
 - ±58-V CAN bus fault tolerant
 - Load dump support on $V_{\mbox{\scriptsize SUP}}$
 - IEC ESD protection
 - Under-voltage protection
 - Thermal shutdown protection
 - TXD dominant state timeout (TXD DTO)
- Available in 14-pin leaded (SOT and SOIC) packages and leadless (VSON) package with wettable flanks for improved automated optical inspection (AOI) capability

2 Applications

- · Body electronics and lighting
- Automotive gateway
- Advanced driver assistance systems (ADAS)
- Infotainment and cluster
- Hybrid, electric & powertrain systems
- · Personal transport vehicles electric bike
- Industrial transportation

3 Description

The TCAN1473-Q1 is a high-speed Controller Area Network (CAN) transceiver that meets the physical layer requirements of the ISO 11898-2:2024 highspeed CAN specification. The device supports both classical CAN and CAN FD data rates up to 8 megabits per second (Mbps).

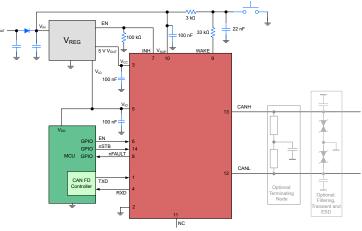
The TCAN1473-Q1 allows for system-level reductions in battery current consumption by selectively enabling the various power supplies that may be present on a system via the INH output pin. This allows a lowcurrent sleep state in which power is gated to all system components except for the TCAN1473-Q1, while monitoring the CAN bus. When a wake-up event is detected, the TCAN1473-Q1 initiates system startup by driving INH high.

Package Information

PART NUMBER	BER PACKAGE ⁽¹⁾ PACKA	
	SOT (DYY)	4.2mm x 2mm
TCAN1473-Q1	SOIC (D)	8.65mm x 6mm
	VSON (DMT)	4.50mm x 3mm

(1) For more information, see Section 11.

(2) The package size (length × width) is a nominal value and includes pins, where applicable.



Simplified Application Schematic





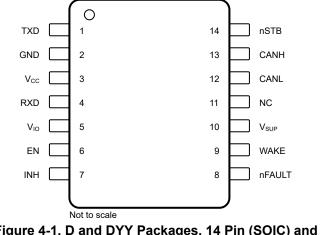
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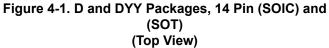
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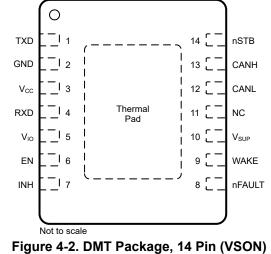
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4 Pin Configuration and Functions







(Top View)

PINS		TYPE ⁽¹⁾	DESCRIPTION		
NAME	NO.	ITPE	DESCRIPTION		
TXD	1	I	CAN transmit data input, integrated pull-up		
GND	2	GND	Ground connection		
V _{CC}	3	Р	5 V transceiver supply		
RXD	4	0	CAN receive data output, tri-state when $V_{IO} < UV_{IO}$		
V _{IO}	5	Р	I/O supply voltage		
EN 6 I		I	Enable input for mode control, integrated pull-down		
INH	7	0	Inhibit pin to control system voltage regulators and supplies, high-voltage		
nFAULT	8	0	Fault output, inverted logic		
WAKE	9	I	Local WAKE input terminal, high voltage		
V _{SUP}	10	Р	High-voltage supply from battery		
NC	11	NC	No connect, internally not connected		
CANL	12	I/O	Low-level CAN bus input/output line		
CANH	13	I/O	High-level CAN bus input/output line		
nSTB	14	I	Standby mode control input, integrated pull-down		
Thermal Pad			Connect the thermal pad to the printed circuit board (PCB) ground plane for thermal relief		

(1) I = input, O = output, P = power, GND = ground, NC = not connected



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{SUP}	Supply voltage ⁽²⁾	-0.3	45	V
V _{CC}	Supply voltage	-0.3	6	V
V _{IO}	Supply voltage I/O level shifter	-0.3	6	V
V _{BUS}	CAN bus I/O voltage (CANH, CANL)	-58	58	V
V _{DIFF}	CAN bus differential voltage (V _{DIFF} = V _{CANH} - V _{CANL})	-58	58	V
V _{WAKE}	WAKE input voltage	-45	45 and V _I ≤ V _{SUP} +0.3	V
V _{INH}	INH pin voltage	-0.3	45 and V _O ≤ V _{SUP} +0.3	V
V _{LOGIC}	Logic pin voltage	-0.3	6	V
I _{O(LOGIC)}	Logic pin output current		8	mA
I _{O(INH)}	Inhibit pin output current		6	mA
I _{O(WAKE)}	WAKE pin output current		3	mA
TJ	Junction temperature	-40	165	°C
T _{STG}	Storage temperature	-65	150	°C

(1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

(2) Able to support load dumps of up to 45 V for 300ms

5.2 ESD Ratings

				VALUE	UNIT
	Human body model (HBM), per AEC	V _{SUP} , CANH, CANL, and WAKE with respect to ground. HBM ESD classification level 3B	± 8000	V	
	Electrostatic discharge		All pins except $V_{\mbox{SUP}},$ CANH, CANL, and WAKE. HBM ESD classification level 3A	± 4000	V
	Charged device model (CDM), per AEC Q100-011	All pins. CDM ESD classification level C5	± 750	V	

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

5.3 ESD Ratings - IEC Specifications

				VALUE	UNIT
V _{ESD}	Electrostatic discharge	CANH, CANL, V_{SUP} , and WAKE terminal to GND	Unpowered Contact Discharge per ISO 10605 ⁽¹⁾	± 8000	v
V _{ESD}	Electrostatic discharge	CANH and CANL terminal to GND	SAE J2962-2 per ISO 10605 Powered Contact Discharge ⁽²⁾	± 8000	V
V _{ESD}	Electrostatic discharge	CANH and CANL terminal to GND	SAE J2962-2 per ISO 10605 Powered Air discharge ⁽²⁾	± 15000	V



5.3 ESD Ratings - IEC Specifications (continued)

				VALUE	UNIT
			Pulse 1	- 100	V
Transient voltage per ISO-7637-2 ⁽¹⁾ CAN, V _{SUP} , WAKE terminal to GND	Pulse 2	75	V		
	ISO-7637-2 ⁽¹⁾	Pulse 3a	- 150	V	
VTRAN			Pulse 3b	100	V
	Transient voltage per ISO-7637-3 ⁽²⁾	CAN terminal to GND	Direct coupling capacitor "slow transient pulse" with 100 nF coupling capacitor - powered	± 30	V

(1) Results given here are specific to the IEC 62228-3 Integrated circuits – EMC evaluation of transceivers – Part 3: CAN transceivers. Testing performed by IBEE Zwickau, EMC report available upon request.

(2) Results given here are specific to the SAE J2962-2 Communication Transceivers Qualification Requirements - CAN. Testing performed by OEM-approved independent 3rd party, EMC report available upon request.

5.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM MA	X UNIT
V _{SUP}	Supply voltage	4.5	4	0 V
V _{IO}	I/O supply voltage	1.7	5	5 V
V _{CC}	CAN transceiver supply voltage	4.75	5.2	5 V
I _{OH(DO)}	Digital output high-level current	-2		mA
I _{OL(DO)}	Digital output low-level current			2 mA
I _{O(INH)}	Inhibit output current			4 mA
TJ	Operating junction temperature	-40	15	0 °C
T _{SDR}	Thermal shutdown	175		°C
T _{SDF}	Thermal shutdown release	160		°C
T _{SD(HYS)}	Thermal shutdown hysteresis		10	°C

5.5 Thermal Information

	THERMAL METRIC (1)	TCAN1473-Q1			
		D (SOIC)	DMT (VSON)	DYY (SOT)	
R _{OJA}	Junction-to-ambient thermal resistance	87.1	39.7	91.0	°C/W
R _{OJC(top)}	Junction-to-case (top) thermal resistance	41.8	41.1	41.7	°C/W
R _{ØJB}	Junction-to-board thermal resistance	43.7	15.9	25.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	8.5	0.9	25.4	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	43.3	15.9	1.1	°C/W
R _{OJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	6.6	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

5.6 Power Dissipation Ratings

PARAMETER		TEST CONDITIONS	POWER DISSIPATION	UNIT
D		V_{SUP} = 14 V, V_{CC} = 5 V, V_{IO} = 5 V, T_J = 27°C, R_L = 60 Ω , nSTB = 5 V, EN = 5 V, $C_{L,RXD}$ = 15 pF. Typical CAN operating conditions at 500 kbps with 25% transmission (dominant) rate.	62	mW
PD	Average power dissipation	$ \begin{array}{l} V_{SUP} = 14 \text{ V}, V_{CC} = 5.5 \text{ V}, V_{IO} = 5.5 \text{ V}, T_J = 150^{\circ}\text{C}, R_L = \\ 50 \ \Omega, \text{ nSTB} = 5.5 \text{ V}, \text{EN} = 5.5 \text{ V}, \text{C}_{L,RXD} = 15 \text{ pF}. \text{ Typical} \\ \text{high load CAN operating conditions at 1 Mbps with 50\% } \\ \text{transmission (dominant) rate and loaded network.} \end{array} $	135	mW



5.7 Power Supply Characteristics

Over recommended operating conditions with $T_J = -40^{\circ}$ C to 150°C, unless otherwise noted. All typical values are taken at 25°C, $V_{SUP} = 12$ V, $V_{IO} = 3.3$ V, $V_{CC} = 5$ V and $R_L = 60 \Omega$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Supply Voltage a	nd Current Characteristics					
SUP_NORMAL	Supply current CAN active	Normal mode, silent mode, and go-to-sleep mode			140	μA
SUP_STBY	Supply current, Standby mode CAN autonomous: inactive	Standby mode ⁽²⁾			50	μA
SUP_SLEEP	Supply current CAN autonomous: inactive	Sleep mode		18	30	μA
SUP_BIAS	Supply current Additional current when in CAN autonomous: active	5.5 V < $V_{SUP} \le 28 V^{(1)}$			60	μA
UV _{SUP(R)}	Undervoltage V _{SUP} threshold rising	Ramp up	3.85		4.4	V
UV _{SUP(F)}	Undervoltage V _{SUP} threshold falling	Ramp down	3.5		4.25	V
	Supply current CAN active: dominant	Normal mode $TXD = 0 V, R_L = 60 \Omega, C_L = open$ See Figure 6-3			60	mA
CC_NORMAL	Supply current CAN active: dominant	Normal mode TXD = 0 V, R _L = 50 Ω , C _L = open			70	mA
	V _{CC} supply current normal mode Dominant with bus fault	Normal mode TXD = 0 V, R_L = open, C_L = open, CANH = -25 V			110	mA
I _{CC_NORMAL}	Supply current CAN active: recessive	Normal mode TXD = V_{IO} , R_L = 50 Ω , C_L = open			5	mA
сс_ѕтву	Supply current CAN autonomous: inactive	Standby mode, T _J = -40 °C to 85 °C EN = nSTB = 0 V			2	μΑ
Ісс_ѕтву	Supply current CAN autonomous: inactive	Standby mode EN = nSTB = 0 V			5	μΑ
ICC_SILENT	Supply current	Silent and go-to-sleep mode TXD = nSTB = V_{IO} , R_L = 50 Ω , C_L = open			2.5	mA
	Supply current CAN autonomous: inactive	Sleep mode, T_J = -40 °C to 85 °C EN = 0 V or V _{IO} , nSTB = 0 V			2	μΑ
ICC_SLEEP	Supply current CAN autonomous: inactive	Sleep mode EN = 0 V or V _{IO} , nSTB = 0 V			5	μΑ
UV _{CC(R)}	Undervoltage V _{CC} threshold rising	Ramp up		4.1	4.4	V
JV _{CC(F)}	Undervoltage V _{CC} threshold falling	Ramp down	3.5	3.9		V
HYS(UVCC)	Hysteresis voltage on UV _{CC}		50	250	320	mV
	I/O supply current	Normal mode RXD floating, TXD = 0 V			350	μA
IO_NORMAL	I/O supply current	Normal mode, standby mode, or go-to-sleep mode RXD floating, TXD = V _{IO}			5	μA
	I/O supply current	Sleep mode, T _J = -40 °C to 85 °C nSTB = 0 V			2.5	μA
IIO_SLEEP	I/O supply current	Sleep mode nSTB = 0 V			5	μA
UV _{IO(R)}	Under voltage V_{IO} threshold rising	Ramp up		1.4	1.65	V
UV _{IO(F)}	Under voltage V _{IO} threshold falling	Ramp down	1	1.25		V
V _{HYS(UVIO)}	Hysteresis voltage on UV _{IO}		30	60	160	mV

I_{SUP(BIAS)} is calculated by subtracting the supply current in CAN autonomous inactive mode from the total supply current in CAN autonomous active mode



(2) After a valid wake-up, the CAN transceiver switches to CAN autonomous active mode and the I_{SUP(BIAS)} current needs to be added to the specified I_{SUP} current in CAN autonomous inactive mode.

5.8 Electrical Characteristics

Over recommended operating conditions with $T_J = -40^{\circ}C$ to 150°C, unless otherwise noted. All typical values are taken at 25°C, $V_{SUP} = 12$ V, $V_{IO} = 3.3$ V, $V_{CC} = 5$ V and $R_L = 60 \Omega$

VCANL(D) Bus VCANL(D) Bus VCANH(R) Rect VCANL(R) Bus VCANL(R) Bus VSYM Drive VSYM Drive VSYM DC I VSYM_DC DC I VDIFF(D) Bus VDIFF(R) Bus VDIFF(R) Bus VDIFF(R) Bus VOIFF(R) Bus	acteristics s output voltage (dominar s output voltage (dominar s output voltage (dominar cessive output voltage s biasing active cessive output voltage s biasing active ver symmetry s biasing active $O(CANH) + VO(CANL)) / VCC$ C Driver symmetry s biasing active $C - VO(CANH) - VO(CANL)$ ferential output voltage s biasing active minant	rt) CANL Recessive output voltage Bus biasing active	$\begin{array}{l} TXD=0\ V,\ 45\leqR_{L}\leq65\ \Omega,\ C_{L}=open,\ R_{CM}=\\ open\\ See\ Figure\ 6\text{-1}\ and\ Figure\ 6\text{-4}\\ \\ TXD=V_{IO},\ R_{L}=open\ (no\ load),\ R_{CM}=open\\ See\ Figure\ 6\text{-1}\ and\ Figure\ 6\text{-4}\\ \\ TXD=V_{IO},\ 45\leqR_{L}\leq65\ \Omega,\ C_{L}=open,\ C_{SPLIT}\\ see\ Figure\ 6\text{-1}\ and\ Figure\ 6\text{-4}\\ \\ nSTB=V_{IO},\ R_{L}=45\leqR_{L}\leq65\ \Omega,\ C_{SPLIT}=4.7\\ nF,\ C_{L}=Open,\ R_{CM}=Open,\ TXD=250\ kHz,\\ 1\ MHz,\ 2.5\ MHz\\ \\ See\ Figure\ 6\text{-1}\ and\ Figure\ 6\text{-4}\\ \\ nSTB=V_{IO},\ R_{L}=45\leqR_{L}\leq65\ \Omega,\ C_{L}=open\\ \\ \\ See\ Figure\ 6\text{-1}\ and\ Figure\ 6\text{-4}\\ \\ \\ nSTB=V_{IO},\ TXD=0\ V,\ 45\ \Omega\leqR_{L}\leq65\ \Omega,\ C_{L}=\\ \\ \\ open\\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ $	3 0.75 2 2.256 0.95 300	4.26 2.01 3 2.756 1.05 300	V V V V V/V
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VCANH(R) Rect VCANL(R) Bus VCANH(R) Rect VCANH(R) Bus VCANH(R) Bus VSYM Drive VSYM Drive VSYM Drive VSYM_DC DC I Bus Vcc VDIFF(D) Diffe VDIFF(R) Bus VDIFF(R) Bus VDIFF(R) Bus VOIFF(R) Bus	cessive output voltage s biasing active cessive output voltage s biasing active ver symmetry s biasing active $D(CANH) + VO(CANL)) / V_{CC}$ C Driver symmetry s biasing active c - VO(CANH) - VO(CANL)	Recessive output voltage Bus biasing active	$\begin{array}{l} TXD=V_{IO}, R_{L} = open \ (no \ load), R_{CM} = open \\ See \ Figure \ 6-1 \ and \ Figure \ 6-4 \\ \\ TXD=V_{IO}, 45 \leq R_{L} \leq 65 \ \Omega, \ C_{L} = open, \ C_{SPLIT} \\ = 4.7 \ nF \\ See \ Figure \ 6-1 \ and \ Figure \ 6-4 \\ \\ nSTB=V_{IO}, R_{L} = 45 \leq R_{L} \leq 65 \ \Omega, \ C_{SPLIT} = 4.7 \\ nF, \ C_{L} = Open, \ R_{CM} = Open, \ TXD = 250 \ kHz, \\ 1 \ MHz, 2.5 \ MHz \\ \\ See \ Figure \ 6-1 \ and \ Figure \ 6-4 \\ \\ \\ nSTB=V_{IO}, \ R_{L} = 45 \leq R_{L} \leq 65 \ \Omega, \ C_{L} = open \\ \\ See \ Figure \ 6-1 \ and \ Figure \ 6-4 \\ \\ \\ \\ nSTB = V_{IO}, \ TXD = 0 \ V, 45 \ \Omega \leq R_{L} \leq 65 \ \Omega, \ C_{L} = \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$	2 2.256 0.95 -300	3 2.756 1.05	V V V/V
V _{CANL(R)} Bus V _{CANL(R)} Rect V _{CANL(R)} Bus V _{SYM} Drive Bus (V _{O(} V _{SYM_DC} DC I Bus V _{CC} V _{DIFF(D)} Diffe Bus Dorr V _{DIFF(R)} Bus Rect V _{DIFF(R)} Bus Rect V _{DIFF(R)} Bus	s biasing active cessive output voltage s biasing active ver symmetry s biasing active D(CANH) + VO(CANL) / VCC C Driver symmetry s biasing active C - VO(CANH) - VO(CANL) ferential output voltage s biasing active	voltage Bus biasing active CANH - CANL	$ \begin{array}{l} \label{eq:see Figure 6-1} \text{See Figure 6-1} & \text{TXD} = V_{IO}, 45 \leq R_L \leq 65 \ \Omega, \ C_L = \text{open}, \ C_{SPLIT} \\ = 4.7 \ nF \\ \text{See Figure 6-1} \text{ and Figure 6-4} \\ \\ nSTB = V_{IO}, \ R_L = 45 \leq R_L \leq 65 \ \Omega, \ C_{SPLIT} = 4.7 \\ nF, \ C_L = \text{Open}, \ R_{CM} = \text{Open}, \ TXD = 250 \ \text{kHz}, \\ 1 \ \text{MHz}, 2.5 \ \text{MHz} \\ \text{See Figure 6-1} \text{ and Figure 6-4} \\ \\ nSTB = V_{IO}, \ R_L = 45 \leq R_L \leq 65 \ \Omega, \ C_L = \text{open} \\ \text{See Figure 6-1} \text{ and Figure 6-4} \\ \\ nSTB = V_{IO}, \ TXD = 0 \ V, 45 \ \Omega \leq R_L \leq 65 \ \Omega, \ C_L = \\ \\ \text{open} \end{array} $	2.256 0.95 300	2.756	V V/V
V _{CANH(R)} Rect Bus V _{CANL(R)} Drive Bus V _{SYM} Drive Bus V _{SYM} DC I Bus V _{SYM_DC} DC I Bus V _{DIFF(D)} Diffe Bus Dom V _{DIFF(R)} Diffe Bus Rect V _{DIFF(R)} Diffe Bus Rect V _{DIFF(R)} Diffe Bus Rect	s biasing active ver symmetry s biasing active $p_{(CANH)} + V_{O(CANL)}) / V_{CC}$ c Driver symmetry s biasing active $c - V_{O(CANH)} - V_{O(CANL)}$ ferential output voltage s biasing active	voltage Bus biasing active CANH - CANL	= 4.7 nF See Figure 6-1 and Figure 6-4 nSTB= V_{IO} , $R_L = 45 \le R_L \le 65 \Omega$, $C_{SPLIT} = 4.7$ nF, $C_L = Open$, $R_{CM} = Open$, TXD = 250 kHz, 1 MHz, 2.5 MHz See Figure 6-1 and Figure 6-4 nSTB= V_{IO} , $R_L = 45 \le R_L \le 65 \Omega$, $C_L = open$ See Figure 6-1 and Figure 6-4 nSTB = V_{IO} , TXD = 0 V, 45 $\Omega \le R_L \le 65 \Omega$, $C_L = open$	0.95 300	1.05	V/V
V _{SYM} Bus (V _{O(}) V _{SYM_DC} DC I Bus V _{CC} V _{DIFF(D)} Diffe Bus Dorr V _{DIFF(R)} Diffe Bus Reco V _{DIFF(R)} Diffe	s biasing active $D(CANH) + V_O(CANL)) / V_{CC}$ Driver symmetry s biasing active $C - V_O(CANH) - V_O(CANL)$ ferential output voltage s biasing active		$\begin{array}{l} nF, C_{L} = Open, R_{CM} = Open, TXD = 250 \; kHz, \\ 1 \; MHz, 2.5 \; MHz \\ \texttt{See Figure 6-1} \; \texttt{and Figure 6-4} \\ \\ nSTB = V_{IO}, R_{L} = 45 \leq R_{L} \leq 65 \; \Omega, C_{L} = open \\ \texttt{See Figure 6-1} \; \texttt{and Figure 6-4} \\ \\ \\ nSTB = V_{IO}, TXD = 0 \; V, 45 \; \Omega \leq R_{L} \leq 65 \; \Omega, C_{L} = \\ \\ \\ open \end{array}$	-300		
V _{SYM_DC} Bus V _{CC} V _{DIFF(D)} Diffe Bus Dom V _{DIFF(R)} Bus Rect V _{DIFF(R)} Bus Rect V _{DIFF(R)} Bus	s biasing active $c - V_{O(CANH)} - V_{O(CANL)}$ ferential output voltage s biasing active		See Figure 6-1 and Figure 6-4 $nSTB = V_{IO}, TXD = 0 V, 45 \Omega \le R_L \le 65 \Omega, C_L = open$	·	300	m\/
V _{DIFF(D)} Bus Dom V _{DIFF(R)} Diffe Bus Reco V _{DIFF(R)} Diffe Bus Reco	s biasing active		open			111V
V _{DIFF(D)} Bus Dom V _{DIFF(R)} Diffe Bus Reco V _{DIFF(R)} Diffe Bus Reco	s biasing active	0.000	See Figure 6-1 and Figure 6-4	1.5	3	V
V _{DIFF(R)} Bus Recu V _{DIFF(R)} Bus Recu Volumentaria		CANH - CANL	$\begin{array}{l} \text{nSTB =V_{IO}, TXD = 0 V, 45 } \Omega \leq \text{R}_{L} \leq 70 \ \Omega, \text{ CL}} \\ \text{= open} \\ \text{See Figure 6-1 and Figure 6-4} \end{array}$	1.5	3.3	V
V _{DIFF(R)} Bus Recu V _{DIFF(R)} Bus Recu Volume		CANH - CANL	nSTB =V _{IO} , TXD = 0 V, R _L = 2240 Ω, C _L = open See Figure 6-1 and Figure 6-4	1.5	5	V
V _{DIFF(R)} Bus Reco	ferential output voltage s biasing active cessive	CANH - CANL	$\label{eq:nSTB} \begin{split} &nSTB = V_{IO}, TXD = V_{IO}, 45 \leq R_L \leq 65 \ \Omega, \ C_L = \\ &open, \ C_{SPLIT} = 4.7 \ nF \\ &See \ Figure \ 6-1 \ and \ Figure \ 6-4 \end{split}$	-50	50	mV
	Differential output voltage Bus biasing active CANH - CANL Recessive		$\label{eq:nSTB} \begin{split} &nSTB = V_{IO}, \mbox{ TXD} = V_{IO}, \mbox{ R}_L = \mbox{open} \\ & See \mbox{ Figure 6-1 and Figure 6-4} \end{split}$	-50	50	mV
inac	s output voltage on CANH ctive	l with bus biasing	$\label{eq:rescaled} \begin{array}{l} \text{nSTB =0 V, TXD = V_{IO}, R_L = open (no load),} \\ \text{C}_L = open \\ \text{See Figure 6-1 and Figure 6-4} \end{array}$	-0.1	0.1	V
	s output voltage on CANL ctive	. with bus biasing	$\label{eq:response} \begin{array}{l} \text{nSTB =0 V, TXD = V_{IO}, R_L = open (no load),} \\ \text{C}_L = open \\ \text{See Figure 6-1 and Figure 6-4} \end{array}$	-0.1	0.1	V
	s output voltage on CANF cessive) with bus biasing		$\label{eq:nSTB} \begin{array}{l} \text{nSTB =0 V, TXD = V_{IO}, R_L = open (no load),} \\ C_L = open \\ \text{See Figure 6-1 and Figure 6-4} \end{array}$	-0.2	0.2	V
	ort-circuit steady-state ou minant, CANH	tput current,	$\label{eq:nSTB} \begin{split} &nSTB = V_{IO}, TXD = 0 \ V \\ &-15 \ V \leq V_{(CANH)} \leq 40 \ V \\ See Figure 6-1 \ and Figure 6-8 \end{split}$	-100		mA
	ort-circuit steady-state ou minant, CANL	tput current,	$\label{eq:nSTB} \begin{split} nSTB &= V_{IO,} TXD = 0 \ V \\ -15 \ V &\leq V_{(CANL)} \leq 40 \ V \\ See \ Figure \ 6-1 \ and \ Figure \ 6-8 \end{split}$		100	mA
I _{OS(REC)} Bus	Short-circuit steady-state output current Bus biasing active Recessive		$\label{eq:nSTB} \begin{split} &nSTB = V_{IO}, V_{BUS} = CANH = CANL \\ &-27 \ V \leq V_{BUS} \leq 42 \ V \\ See Figure 6-1 \ and Figure 6-8 \end{split}$	-3	3	mA
Ros Act DEC	gle ended SIC impedanc nmon mode bias and CAI de bias) during active rec ase	NL to common	$2 V \le V_{CANH,CANL} \le VCC - 2 V \text{ if}$ -12 V $\le V_{O(D)} \le 12 V$ See Figure 6-11	37.5	66.5	Ω
R _{DIFF_ACT_RE} Diffe	ferential input resistance i		2 V ≤ V _{CANH,CANL} ≤ VCC - 2 V See Figure 6-11	75	133	Ω

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5.8 Electrical Characteristics (continued)

Over recommended operating conditions with $T_J = -40^{\circ}$ C to 150°C, unless otherwise noted. All typical values are taken at 25°C, $V_{SUP} = 12$ V, $V_{IO} = 3.3$ V, $V_{CC} = 5$ V and $R_L = 60 \Omega$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{IT(DOM)}	Receiver dominant state input voltage range Bus biasing active	nSTB = V _{IO} , -12 V ≤ V _{CM} ≤ 12 V See Figure 6-5 and Table 7-6	0.9		8	V
V _{IT(REC)}	Receiver recessive state input voltage range Bus biasing active		-3		0.5	V
V _{HYS}	Hysteresis voltage for input threshold Bus biasing active	nSTB = V _{IO} See Figure 6-5 and Table 7-6		135		mV
V _{DIFF(DOM)}	Receiver dominant state input voltage range Bus biasing inactive	nSTB = 0 V, -12 V ≤ V _{CM} ≤ 12 V See Figure 6-5 and Table 7-6	1.150		8	V
V _{DIFF(REC)}	Receiver recessive state input voltage range Bus biasing inactive		-3		0.4	V
V _{CM}	Common mode range	nSTB = V _{IO} See Figure 6-5 and Table 7-6	-12		12	V
I _{OFF(LKG)}	Power-off (unpowered) bus input leakage current	V _{SUP} = 0 V, CANH = CANL = 5 V			4.5	μA
Cı	Input capacitance to ground (CANH or CANL)	$TXD = V_{CC} = V_{IO}$			40	pF
C _{ID}	Differential input capacitance (1)	$TXD = V_{CC} = V_{IO}$			20	pF
R _{ID}	Differential input resistance	TXD = V _{CC} = V _{IO} = 5 V, nSTB = 5 V	30		100	kΩ
R _{IN}	Input resistance (CANH or CANL)	$-12 V \le V_{CM} \le 12 V$	15		50	kΩ
R _{IN(M)}	Input resistance matching: [1 – R _{IN(CANH)} / R _{IN(CANL)}] × 100%	$V_{(CANH)} = V_{(CANL)} = 5 V$	-3		3	%
R _{CBF}	Valid differential load impedance range for bus fault circuitry	$R_{CM} = R_L, C_L = open$	45	·	70	Ω
TXD Chara	cteristics					
V _{IH}	High-level input voltage		0.7			V _{IO}
V _{IL}	Low-level input voltage				0.3	V _{IO}
I _{IH}	High-level input leakage current	TXD = V _{IO} = 5.5 V	-2.5		1	μA
IIL	Low-level input leakage current	TXD = 0 V, V _{IO} = 5.5 V	-137		-2.5	μA
I _{LKG(OFF)}	Unpowered leakage current	TXD = 5.5 V, V _{SUP} = V _{IO} = 0 V	-1		1	μA
R _{PU}	Pull-up resistance to V _{IO}		40	60	80	kΩ
Cı	Input Capacitance	$V_{IN} = 0.4 \times \sin(2 \times \pi \times 2 \times 10^6 \times t) + 2.5 V$		5		pF
RXD Chara	cteristics		•			
V _{OH}	High-level output voltage	$I_0 = -2 \text{ mA}$	0.8			V _{IO}
V _{OL}	Low-level output voltage	I _O = 2 mA			0.2	V _{IO}
I _{LKG(OFF)}	Unpowered leakage current	RXD = 5.5 V, V _{SUP} = V _{IO} = 0 V	-1		1	μA
nSTB Char	acteristics					
V _{IH}	High-level input voltage		0.7			V_{IO}
VIL	Low-level input voltage				0.3	V_{IO}
I _{IH}	High-level input leakage current	nSTB = V _{IO} = 5.5 V	0.5		137	μΑ
I _{IL}	Low-level input leakage current	nSTB = 0 V, V _{IO} = 5.5 V	-1		1	μA
I _{LKG(OFF)}	Unpowered leakage current	nSTB = 5.5 V, V _{IO} = 0 V	-1		1	μΑ
R _{PD}	Pull-down resistance to GND		40	60	80	kΩ
nFAULT Ch	aracteristics					
V _{OH}	High-level output voltage	I _O = -2 mA Figure 6-3	0.8			V _{IO}
V _{OL}	Low-level output voltage	I _O = 2 mA			0.2	V _{IO}
I _{LKG(OFF)}	Unpowered leakage current	nFAULT = 5.5 V, V _{IO} = 0 V	-1		1	μA
EN Charact	teristics	•	·			
VIH	High-level input voltage		0.7			VIO

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5.8 Electrical Characteristics (continued)

Over recommended operating conditions with $T_J = -40^{\circ}$ C to 150°C, unless otherwise noted. All typical values are taken at 25°C, $V_{SUP} = 12$ V, $V_{IO} = 3.3$ V, $V_{CC} = 5$ V and $R_L = 60 \Omega$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{IL}	Low-level input voltage				0.3	V _{IO}
I _{IH}	High-level input leakage current	EN = V _{CC} = V _{IO} = 5.5 V	0.5		137	μA
IIL	Low-level input leakage current	EN = 0 V, V _{CC} = V _{IO} = 5.5 V	-1		1	μA
I _{LKG(OFF)}	Unpowered leakage current	EN = 5.5 V, V _{CC} = V _{IO} = 0 V	-1		1	μA
R _{PD}	Pull-down resistance to GND		40	60	80	kΩ
WAKE Cha	racteristics				I	
V _{IH}	High-level input voltage	Sleep mode	V _{SUP} - 2			V
V _{IL}	Low-level input voltage	Sleep mode		V	_{SUP} - 3.5	V
I _{IH}	High-level input leakage current	WAKE = V _{SUP} – 1 V	-3			μA
IIL	Low-level input leakage current	WAKE = 1 V			3	μA
INH Charao	cteristics				I	
ΔV _H	High-level voltage drop from V_{SUP} to INH $\left(V_{SUP} - V_{INH}\right)$	I _{INH} = -6 mA		0.5	1	V
I _{LKG(INH)}	Sleep mode leakage current	INH = 0 V	-0.5		0.5	μA
R _{PD}	Pull-down resistance	Sleep mode	2.5	4	6	MΩ

(1) Specified by design and verified via bench characterization

5.9 Timing Requirements

Over recommended operating conditions with $T_J = -40^{\circ}$ C to 150°C, unless otherwise noted. All typical values are taken at 25°C, $V_{SUP} = 12 \text{ V}$, $V_{IO} = 3.3 \text{ V}$, $V_{CC} = 5 \text{ V}$ and $R_L = 60 \Omega$

	PARA	METER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Supply Charac	teristics					I	
t _{PWRUP}	Time required fo	r INH active after $V_{SUP} \ge UV_{SUP(R)}$	See Figure 6-10		340		μs
t _{UV}	Undervoltage filt	er time V_{CC} and V_{IO} ⁽¹⁾	$V_{CC} \le UV_{CC} \text{ or } V_{IO} \le UV_{IO}$	100		350	ms
t _{UV(RE-ENABLE)}	Re-enable time	after undervoltage event ⁽¹⁾	Time for device to return to normal operation from a ${\rm UV}_{\rm CC}$ or ${\rm UV}_{\rm IO}$ undervoltage event			200	μs
Device Charac	teristics						
t _{PROP(LOOP1)}		driver input (TXD) to receiver ecessive to dominant	R_L = 60 Ω, C_L = 100 pF, $C_{L(RXD)}$ = 15 pF See Figure 6-6		100	190	ns
t _{PROP(LOOP2)}		driver input (TXD) to receiver ominant to recessive	R_L = 60 Ω, C_L = 100 pF, $C_{L(RXD)}$ = 15 pF See Figure 6-6		110	190	ns
t _{WK(TIMEOUT)}	Bus wake-up tim	neout value ⁽¹⁾		0.8		2	ms
t _{WK(FILTER)}	Bus time to mee wake-up reques	t filtered bus requirements for $t^{(1)}$		0.5		0.95	μs
tSILENCE	Timeout for bus	inactivity ⁽¹⁾	Timer is reset and restarted, when bus changes from dominant to recessive or vice versa	0.6		1.2	s
t _{BIAS}	Bus bias reaction time ⁽¹⁾	Measured from the start of a dominant-recessive-dominant sequence (each phase 6 μ s) until V _{SYM} ≥ 0.1	nSTB = EN = 0 V, R_L = 60 Ω , C_{SPLIT} = 4.7 nF See Figure 6-9 and Figure 8-2			200	μs
t _{CBF}	Bus fault-detecti	on time	$45 \le R_{CM} \le 70 \Omega$ $C_L = open$	2.5			μs
t _{WAKE_HT}	Hold time for wh recognize LWU	ich WAKE pin voltage should be sta	able after the rising or falling edge on WAKE pin to	5		50	μs
Mode Change	Characteristics						
t _{INH_SLP_STB}	Time after WUP	or LWU event until INH asserted (1)			100	μs
t _{MODE1}		ne from leaving the Sleep mode to or Silent mode ⁽¹⁾	Time measured from VCC and VIO crossing UV thresholds to entering normal or silent mode.			20	μs
t _{MODE2}		ne between normal, silent and nd from sleep to standby mode ⁽¹⁾	Mode change time between normal, silent and standby mode and from sleep to standby mode			10	μs



5.9 Timing Requirements (continued)

Over recommended operating conditions with $T_J = -40^{\circ}$ C to 150°C, unless otherwise noted. All typical values are taken at 25°C, $V_{SUP} = 12$ V, $V_{IO} = 3.3$ V, $V_{CC} = 5$ V and $R_L = 60 \Omega$

	PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
t _{GOTOSLEEP}	Minimum hold time for transition to sleep mode ⁽¹⁾	EN = H and nSTB = L	20	50	μs

(1) Specified by design and verified via bench characterization

5.10 Switching Characteristics

Over recommended operating conditions with T_J = -40°C to 150°C, unless otherwise noted. All typical values are taken at 25°C, V_{SUP} = 12 V, V_{IO} = 3.3 V, V_{CC} = 5 V and R_L = 60 Ω

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Driver Chara	cteristics					
t _{prop(TxD-} busdom)	Propagation delay time, high-to-low TXD edge to bus dominant (recessive to dominant)	R _L = 60 Ω, C _L = 100 pF, R _{CM} = open			80	ns
t _{prop(TxD-} busrec)	Propagation delay time, low-to-high TXD edge to bus recessive (dominant to recessive)	See Figure 6-4			80	ns
t _{sk(p)}	Pulse skew (t _{prop(TxD-busdom)} - t _{prop(TxD-busrec)})			3		ns
t _R	Differential output signal rise time	R_L = 60 Ω, C_L = 100 pF, R_{CM} = open See Figure 6-4		25		ns
t _F	Differential output signal fall time			25		ns
t _{TXDDTO}	Dominant timeout	TXD = 0 V, R_L = 60 Ω , C_L = open See Figure 6-7	1.2		3.8	ms
Receiver Cha	racteristics	- I			I	
t _{prop(busdom-} RxD)	Propagation delay time, bus dominant input to RxD low output	C _{L(RXD)} = 15 pF			110	ns
t _{prop(busrec-} RxD)	Propagation delay time, bus to recessive input to RXD high output	See Figure 6-5			110	ns
t _R	Output signal rise time (RXD)	C _{L(RXD)} = 15 pF		3		ns
t _F	Output signal fall time (RXD)	See Figure 6-5		3		ns
t _{BUSDOM}	Dominant time out	$R_L = 60 \Omega$, $C_L = open$ See Figure 6-7	1.4		3.8	ms
CAN FD Sign	al Improvement Characteristics					
tpas_rec_sta rt	Start time of passive recessive phase	$\label{eq:response} \begin{array}{l} R_{L} = 45 \text{ to } 65 \ \Omega, \ C_{L1} = \text{open}, \ C_{L2} = \\ 100 \ pF, \ C_{L(RXD)} = 15 \ pF \\ \text{Measured from rising TXD edge with} < \\ 5\text{ns slope at } 50\% \ \text{threshold}, \ \text{to the end} \\ \text{of the signal improvement phase;} \\ R_{DIFF_PAS_REC} \geq MIN \ R_{DIFF_ACT_REC}; \\ R_{SE_CANH/L} \geq MIN \ R_{SE_SIC_REC} \end{array}$			530	ns
tsic_start	Start time of active signal improvement phase	$ \begin{array}{l} R_{L} = 45 \text{ to } 65 \ \Omega, \ C_{L1} = \text{open}, \ C_{L2} = \\ 100 \ pF, \ C_{L(RXD)} = 15 \ pF \\ \text{Measured from rising TXD edge with <} \\ 5 \text{ns slope at } 50\% \ \text{threshold to the start} \\ \text{of active signal improvement phase} \end{array} $			120	ns
t _{SIC_END}	End time of active signal improvement phase	$ \begin{array}{l} R_{L} = 45 \text{ to } 65 \ \Omega, \ C_{L1} = \text{open}, \ C_{L2} = \\ 100 \ pF, \ C_{L(RXD)} = 15 \ pF \\ \text{Measured from rising TXD edge with } < \\ 5 \text{ns slope at } 50\% \text{ threshold to the end} \\ \text{of active signal improvement phase} \end{array} $	355			ns
$t_{\Delta Bit(Bus)}$	Transmitted bit width variation	$ \begin{array}{l} \text{Bus recessive bit length variation} \\ \text{relative to TxD bit length,} \\ \text{see Figure 6-6 } t_{\Delta Bit(Bus)} = t_{Bit(Bus)} - \\ t_{Bit(TxD)}, t_{Bit(TxD)} >= 200 \text{ ns} \\ \text{R}_{L} = 45 \text{ to } 65 \ \Omega, \ \text{C}_{L1} = \text{open, } \text{C}_{L2} = \\ 100 \text{ pF, } \text{C}_{L(RXD)} = 15 \text{ pF} \end{array} $	-10		10	ns
$t_{\Delta Bit(RxD)}$	Received bit width variation	$ \begin{array}{l} \text{RxD recessive bit length variation} \\ \text{relative to TXD bit length,} \\ \text{see Figure 6-6} t_{\Delta Bit(RxD)} = t_{Bit(RxD)} - t_{Bit(TxD)}, t_{Bit(TxD)} >= 200 \text{ ns} \\ \text{R}_L = 45 \text{ to } 65 \ \Omega, \ \text{C}_{L1} = \text{ open, } \text{C}_{L2} = 100 \text{ pF, } \text{C}_{L(RXD)} = 15 \text{ pF} \end{array} $	-30		20	ns

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5.10 Switching Characteristics (continued)

Over recommended operating conditions with $T_J = -40^{\circ}C$ to 150°C, unless otherwise noted. All typical values are taken at 25°C, $V_{SUP} = 12$ V, $V_{IO} = 3.3$ V, $V_{CC} = 5$ V and $R_L = 60 \Omega$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{AREC}	Receiver timing symmetry	$\begin{array}{l} \text{RXD recessive bit length variation} \\ \text{relative to bus bit length,} \\ \text{see Figure 6-6 } t_{\Delta REC} = t_{\text{Bit}(RXD)} \text{-} \\ t_{\text{Bit}(Bus)}, t_{\text{Bit}(TXD)} \text{>= 200 ns} \\ \text{R}_L = 45 \text{ to } 65 \ \Omega, \ C_{L1} = \text{open, } C_{L2} = \\ 100 \text{ pF, } C_{L(RXD)} = 15 \text{ pF} \end{array}$	-20		15	ns



6 Parameter Measurement Information

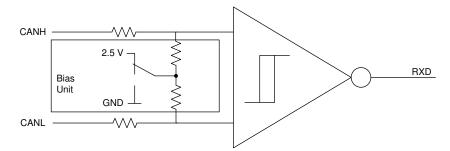


Figure 6-1. Common-Mode Bias Unit and Receiver

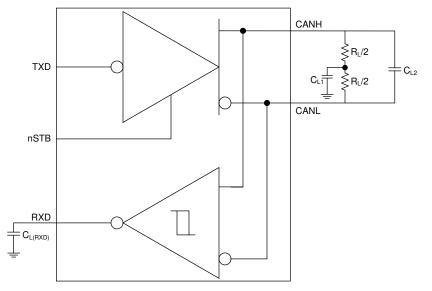


Figure 6-2. Test Circuit

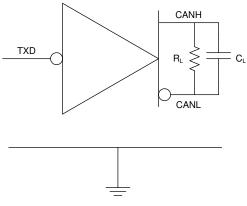


Figure 6-3. Supply Test Circuit



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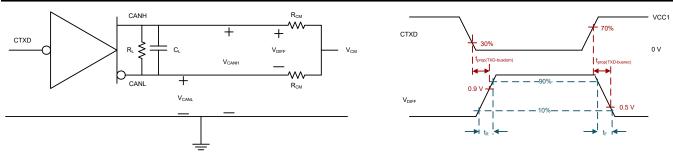


Figure 6-4. Driver Test Circuit and Measurement

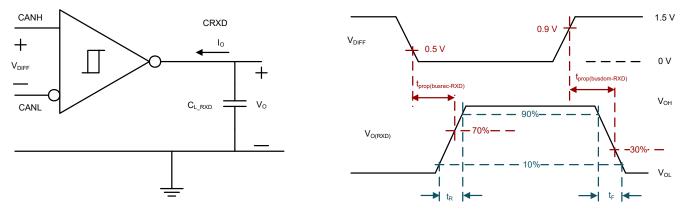


Figure 6-5. Receiver Test Circuit and Measurement

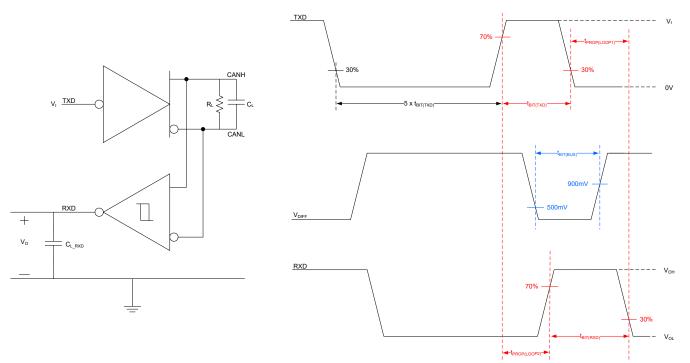


Figure 6-6. Transmitter and Receiver Timing Behavior Test Circuit and Measurement

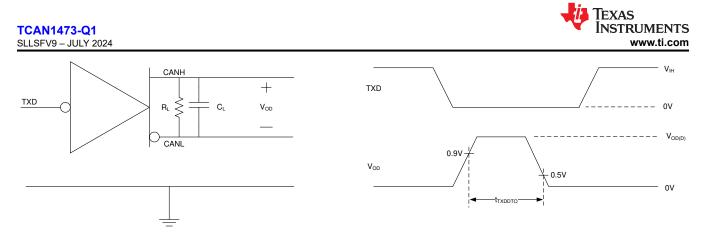


Figure 6-7. TXD Dominant Time Out Test Circuit and Measurement

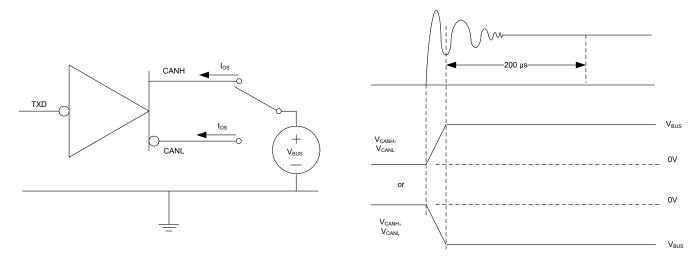


Figure 6-8. Driver Short-Circuit Current Test and Measurement

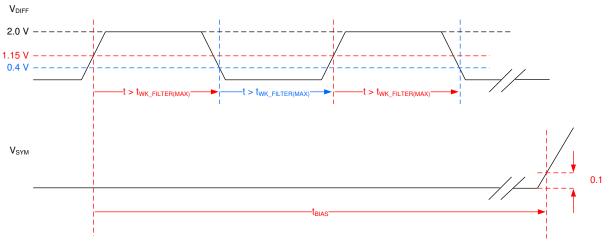
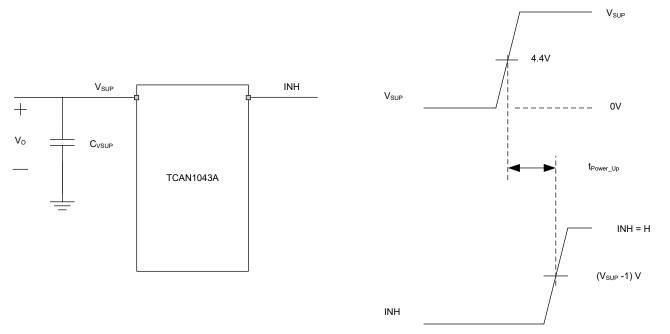


Figure 6-9. Bias Reaction Time Measurement



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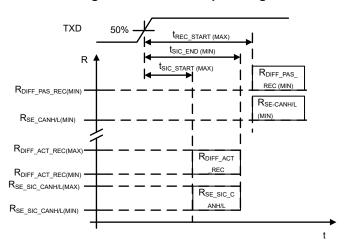


Figure 6-11. SIC Timing and impedance during the active and passive recessive phase



7 Detailed Description

7.1 Overview

The TCAN1473-Q1 is a high-speed Controller Area Network (CAN) transceiver that meets the physical layer requirements of the ISO 11898-2:2024 for CAN-FD and Signal Improvement Capability. and CiA 601-4 high speed CAN specifications. The TCAN1473-Q1 is data rate agnostic making it backward compatible for supporting classical CAN applications while also supporting CAN FD networks up to 8 megabits per second (Mbps).

The transceiver has three separate supply inputs, V_{SUP} , V_{CC} , and V_{IO} . By using V_{IO} , the TCAN1473-Q1 can interface directly to a 1.8V, 2.5V, 3.3V, or 5V controller without the need for a level shifter. The TCAN1473-Q1 allows for system-level reductions in battery current consumption by selectively enabling the various power supplies that may be present in the system via the INH output pin. This enables a low-current sleep state in which power is gated to all system components except for the TCAN1473-Q1, which remains in a low-power state while monitoring the CAN bus. When a wake-up pattern is detected on the bus or when a local wake up is requested via the WAKE input, the device initiates node start-up by driving INH high.

The TCAN1473-Q1 includes many protection and diagnostic features including undervoltage detection, CAN bus fault detection, battery connection detection, thermal shutdown (TSD), driver dominant timeout (TXD DTO), and bus fault protection up to ±58V.

7.1.1 Signal Improvement

The TCAN1473-Q1 includes the Signal Improvement Capability (SIC) that enhances the maximum data rate achievable in complex star topologies by minimizing signal ringing. Signal ringing is the result of reflections caused by impedance mismatch at various points in a complex CAN network.

An example of a star network is shown Figure 7-1.

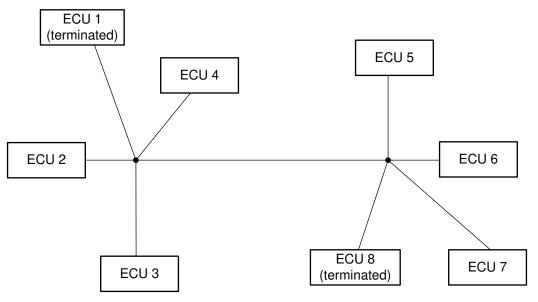


Figure 7-1. CAN network: Star Topology

Recessive-to-dominant signal edge is usually clean as it's strongly driven by the transmitter. Transmitter output impedance of CAN transceiver is $R_{ID(dom)}$ and matches to the network characteristic impedance. For a regular CAN FD transceiver, dominant-to-recessive edge is when the driver output impedance goes to approximately 60k Ω and signal reflected back experiences impedance mismatch which causes ringing. The TCAN1473-Q1 resolves this issue by TX-based Signal improvement capability (SIC). The TCAN1473-Q1 continues to drive the bus recessive strongly for $t_{SIC_TX_base}$ to minimize the reflections, and the recessive bit is clean at the sampling point. In the active recessive phase, transmitter output impedance is low ($R_{ID(active_rec})$). After this phase, the device enters into a passive recessive phase where the driver goes into high impedance state. This



phenomenon is explained using Figure 7-2. For further information, please refer to the white paper on how SIC unlocks the real potential of CAN-FD transceivers.

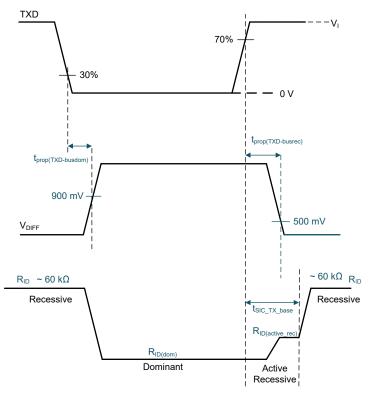


Figure 7-2. TX based Signal Improvement Capability



7.2 Functional Block Diagram

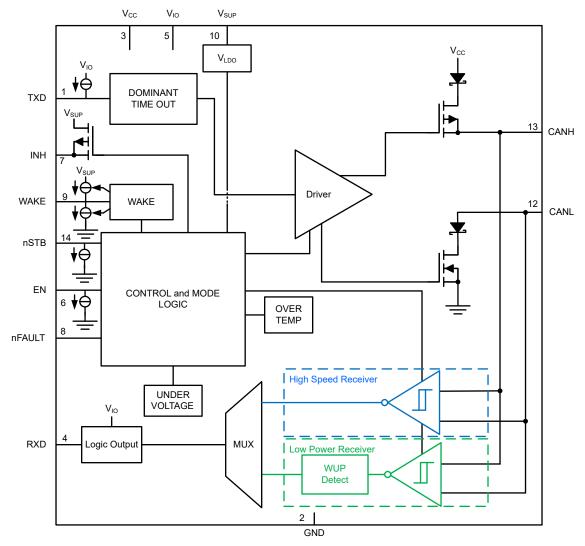


Figure 7-3. TCAN1473-Q1 Functional Block Diagram



7.3 Feature Description

7.3.1 Supply Pins

The TCAN1473-Q1 implements three independent supply inputs for regulating different portions of the device.

7.3.1.1 V_{SUP} Pin

This pin is connected to the battery supply. The pin provides the supply to the internal regulators that support the digital core and the low power CAN receiver.

7.3.1.2 V_{CC} Pin

This pin provides the 5V supply voltage for the CAN transceiver.

7.3.1.3 V_{IO} Pin

This pin provides the digital I/O voltage to match the CAN FD controller I/O voltage. It supports I/O voltages from 1.7V to 5.5V providing a wide range of controller support.

7.3.2 Digital Inputs and Outputs

7.3.2.1 TXD Pin

TXD is a logic-level input signal, referenced to V_{IO} , from a CAN FD controller to the TCAN1473-Q1. TXD is biased to the V_{IO} level to force a recessive input in case the pin floats.

7.3.2.2 RXD Pin

RXD is a logic-level signal output, referenced to V_{IO} , from the TCAN1473-Q1 to a CAN FD controller. The RXD pin is driven to the V_{IO} level as logic-high outputs once a valid V_{IO} is present.

When a power-on or wake-up event takes place, the RXD pin is pulled low.

7.3.2.3 nFAULT Pin

nFAULT is a logic-level output signal, referenced to V_{IO} , from the TCAN1473-Q1 to a CAN FD controller. The nFAULT output is driven to the V_{IO} level as logic-high output.

The nFAULT output is used to transmit the TCAN1473-Q1 status indicator flags to the CAN FD controller. Please see Table 7-1 for the specific fault scenarios that are indicated externally via the nFAULT pin.

7.3.2.4 EN Pin

EN is a logic-level input signal, referenced to V_{IO} , from a CAN FD controller to the TCAN1473-Q1. The EN input pin is for mode selection in conjunction with the nSTB pin. EN is internally pulled low to prevent excessive system power and false wake-up events.

7.3.2.5 nSTB Pin

nSTB is a logic-level input signal, referenced to V_{IO} , from a CAN FD controller to the TCAN1473-Q1. The nSTB input pin is for mode selection in conjunction with the EN pin. nSTB is internally pulled low to prevent excessive system power and false wake-up events.

7.3.3 GND

GND is the ground pin of the transceiver, it must be connected to the PCB ground.

7.3.4 INH Pin

The INH pin is a high-voltage output. It can be used to control external regulators. These regulators are usually used to support the microprocessor and V_{IO} pin. The INH function is on in all modes except for sleep mode. In sleep mode, the INH pin is turned off, going into a high-impedance state. This allows the node to be placed into the lowest power state while in sleep mode. A $100k\Omega$ load can be added to the INH output for a fast transition time from the driven high state to the low state and to force the pin low when left floating.

This terminal should be considered a high-voltage logic terminal, not a power output. The INH pin should be used to drive the EN terminal of the system power management device, and is not used as a switch for the



power management supply itself. This terminal is not reverse-battery protected, and must not be connected outside the system module.

7.3.5 WAKE Pin

The WAKE pin is a high-voltage reverse-blocked input used for the local wake-up (LWU) function. The WAKE pin is bi-directional edge-triggered and recognizes a local wake-up (LWU) on either a rising or falling edge of WAKE pin transition. The LWU function is explained further in the Local Wake-Up (LWU) via WAKE Input Terminal section.

7.3.6 CAN Bus Pins

These are the CAN high and CAN low, CANH and CANL, differential bus pins. These pins are internally connected to the CAN transceiver and the low-voltage wake receiver.

7.3.7 Faults

7.3.7.1 Internal and External Fault Indicators

The following device status indicator flags are implemented to allow for the MCU to determine the status of the device and the system. In addition to faults, the nFAULT terminal also signals wake-up requests and a *cold* power-up sequence on the V_{SUP} battery terminal so the system can do any diagnostics or cold booting sequence necessary. The RXD terminal indicates wake-up request and the faults are multiplexed (ORed) to the nFAULT output.



EVENT	FLAG NAME	CAUSE	INDICATORS ⁽¹⁾	FLAG IS CLEARED	COMMENT
Power-up	PWRON	Power up on V_{SUP} and any return of V_{SUP} after it has been below UV_{SUP}	nFAULT = low upon entering silent mode from standby or sleep mode	After a transition to normal mode	A cold start condition generates a local wake-up WAKERQ, <i>WAKESR</i> and a PWRON flag.
Wake-up Request	WAKERQ ⁽²⁾		nFAULT = RXD = low after wake-up upon entering standby mode	$\begin{array}{l} \mbox{After a transition to normal} \\ \mbox{mode} \\ \mbox{or } V_{CC} < UV_{CC(F)} \\ \mbox{or } V_{IO} < UV_{IO(F)} \mbox{ for } t \geq t_{UV} \end{array}$	Wake-up request may only be set from standby, go-to-sleep, or sleep mode. Resets timers for UV_{VCC} or UV_{VIO}.
Wake-up Source Recognition ⁽³⁾	WAKESR	Wake-up event on CAN bus, state transition on WAKE pin, or initial power up	Available upon entering normal mode ⁽⁴⁾ nFAULT = low indicates a local wake-up event from the WAKE pin nFAULT = high indicates a remote wake-up event from the CAN bus	After four recessive-to- dominant edges on TXD in normal mode, leaving normal mode, or $V_{CC} < UV_{CC(F)}$ or $V_{IO} < UV_{IO(F)}$ for $t \ge t_{UV}$	A cold start condition generates a local wake-up WAKERQ, <i>WAKESR</i> and a PWRON flag.
INH_MASK Change	INHMASK	INH_MASK value changed	nFAULT = low after entering silent mode	A mode transition into normal, standby, go-to-sleep, or sleep modes	To use nFAULT as the flag indicator, nFAULT must be high before initiating change in state of INH_MASK (e.g. there should be no pre-existing faults)
	UV _{CC}	$V_{CC} < UV_{CC(F)}$	Not externally indicated	V _{CC} > UV _{CC(R),} or a wake-up request occurs	
Undervoltage	UVIO	$V_{IO} < UV_{IO(F)}$	Not externally indicated	V _{IO} > UV _{IO(R),} or a wake-up request occurs	
	UV _{SUP}	$V_{SUP} < UV_{SUP(F)}$	Not externally indicated	V_{SUP} > UV _{SUP(R)}	A V_{SUP} undervoltage event generates a cold start condition once V_{SUP} > UV _{SUP(R)}
CAN Bus Fault	CBF	See CAN Bus Fault	nFAULT = low in normal mode only ⁽⁵⁾	Upon leaving normal mode, or if no CAN bus fault is detected for four consecutive dominant-to- recessive transitions of the TXD pin while in normal mode	CAN bus fault must persist for four consecutive dominant- to-recessive transitions
Local Faults	ΤΧΦΦΤΟ	TXD dominant time out, dominant (low) signal for t \geq t_{TXDDTO}	nFAULT = low upon entering silent mode from normal mode	RXD = low & TXD = high, TXD = high & a mode transition into normal, standby, go-to-sleep, or sleep	CAN driver remains disabled until the <i>TXDDTO</i> is cleared. CAN receiver remains active during the TXDDTO fault
	TXDRXD	TXD and RXD pins are shorted together for $t \ge t_{TXDDTO}$	-	modes	CAN driver remains disabled until the <i>TXDRXD</i> is cleared. CAN receiver remains active during the TXDRXD fault
	CANDOM	CAN bus dominant fault, when dominant bus signal received for t ≥ t _{BUSDOM}		RXD = high, or a transition into normal, standby, go-to-sleep, or sleep modes	CAN driver remains enabled during CANDOM fault
	TSD	Thermal shutdown, $T_J \ge T_{SDR}$		$\begin{array}{l} T_J < T_{SDF} \text{ and} \\ RXD = \text{low } \& \text{TXD} = \text{high}, \\ \text{or transition into normal}, \\ \text{standby, go-to-sleep, or sleep} \\ \text{modes} \end{array}$	CAN driver remains disabled until the <i>TSD</i> event is cleared

Table 7-1. TCAN1473-Q1 Transceiver Status Indicator

(1) V_{IO} and V_{SUP} are present

(2) Transitions to go-to-sleep mode is blocked until WAKERQ flag is cleared

(3) Wake-up source recognition reflects the first wake up source. If additional wake-up events occur the source still indicates the original wake-up source

(4) Indicator is only available in normal mode until the flag is cleared

(5) CAN Bus failure flag is indicated after four dominant-to-recessive edges on TXD

7.3.7.1.1 Power-Up (PWRON Flag)

This is an internal and external flag that can be used to control the power-up sequence of the system. When a new battery connection to the transceiver is made the *PWRON* flag is set signifying a cold start condition. The TCAN1473-Q1 treats any undervoltage conditions on the V_{SUP} , $V_{SUP} < UV_{SUP(F)}$, as a cold start. Therefore, when the $V_{SUP} > UV_{SUP(R)}$ condition is met the TCAN1473-Q1 sets the *PWRON* flag which can be used by the system to enter a routine that is only called upon in cold start situations. The *PWRON* flag is indicated by nFAULT driven low after entering silent mode from either standby mode or sleep mode. This flag is cleared after a transition to normal mode.



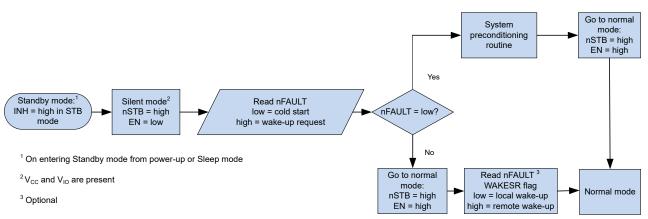


Figure 7-4. Distinguishing between PWRON and Wake Request by Entering Silent Mode

7.3.7.1.2 Wake-Up Request (WAKERQ Flag)

This is an internal and external flag that can be set in standby, go-to-sleep, or sleep mode. This flag is set when either a valid local wake-up (LWU) request occurs, or a valid remote wake request occurs, or on power up on V_{SUP} . The setting of this flag clears the t_{UV} timer for the UV_{CC} or UV_{IO} fault detection. This flag is cleared upon entering normal mode or during an undervoltage event on V_{CC} or V_{IO} .

7.3.7.1.3 Undervoltage Faults

The TCAN1473-Q1 device implements undervoltage detection circuits on all supply terminals: V_{SUP}, V_{CC}, and V_{IO}. The undervoltage flags are internal indicator flags and are not indicated on the nFAULT output pin.

7.3.7.1.3.1 Undervoltage on V_{SUP}

 UV_{SUP} is set when the voltage on V_{SUP} drops below the undervoltage detection voltage threshold, UV_{SUP} . The PWRON and WAKERQ flags are set once $V_{SUP} > UV_{SUP(R)}$.

7.3.7.1.3.2 Undervoltage on V_{CC}

 UV_{CC} is set when the voltage on V_{CC} drops below the undervoltage detection voltage threshold, UV_{CC} , for longer than the t_{UV} undervoltage filter time.

7.3.7.1.3.3 Undervoltage on V_{IO}

 UV_{IO} is set when the voltage on V_{IO} drops below the undervoltage detection voltage threshold, UV_{IO} , for longer than the t_{UV} undervoltage filter time.

7.3.7.1.4 CAN Bus Fault (CBF Flag)

The TCAN1473-Q1 device can detect the following six fault conditions and set the nFAULT pin low as an interrupt so that the controller can be notified and act if a CAN bus fault exists. These failures are detected while transmitting a dominant signal on the CAN bus. If one of these fault conditions persists for four consecutive dominant-to-recessive bit transitions, the nFAULT indicates a CAN bus failure flag in Normal mode by driving the nFAULT pin low. The CAN bus driver remains active. Table 7-2 shows what fault conditions can be detected by the TCAN1473-Q1.

FAULT	Condition						
1	CANH Shorted to V _{BAT}						
2	CANH Shorted to V _{CC}						
3	CANH Shorted to GND						
4	CANL Shorted to V _{BAT}						
5	CANL Shorted to V _{CC}						
6	CANL Shorted to GND						

Table 7-2. Bus Fault Pin State and Detection Table



Bus fault detection is a system level situation. If the fault is occurring at the ECU, the general communication of the bus may be compromised. Until a diagnostic determination can be made, the transceiver remains in CAN active mode during a CAN bus fault enabling the ECU to transmit data to the CAN bus and receive data from the CAN bus. For complete coverage of a node, a system level diagnostic step should be performed for each node and the information should be communicated back to a central point.

While in normal mode, if no CAN bus fault is detected for four consecutive dominant-to-recessive transitions on the TXD pin then the CBF flag is cleared and nFAULT is driven high. The bus fault failure circuitry is able to detect bus faults for a range of differential resistance loads (R_{CBF}) and for any time greater than t_{CBF} .

7.3.7.1.5 TXD Dominant State Timeout (TXDDTO Flag)

TXDDTO is an external flag that is set if the TXD pin is held dominant for t > t_{TXDDTO} . If a TXD DTO condition exists, the nFAULT pin is driven low upon entering silent mode from normal mode. The *TXDDTO* flag is cleared on the next dominant-to-recessive transition on TXD or upon a transition into normal, standby, go-to-sleep, or sleep modes.

7.3.7.1.6 TXD Shorted to RXD Fault (TXDRXD Flag)

TXDRXD is an external flag that is set if the transceiver detects that the TXD and RXD lines have been shorted together for $t \ge t_{TXDDTO}$. If a *TXDRXD* condition exists the nFAULT pin is driven low upon entering silent mode from normal mode and the CAN bus driver is disabled until the *TXDRXD* fault is cleared. The *TXDRXD* flag is cleared on the next dominant-to-recessive transition with TXD high and RXD low or upon a transition into normal, standby, go-to-sleep, or sleep modes.

7.3.7.1.7 CAN Bus Dominant Fault (CANDOM Flag)

CANDOM is an external flag that is set if the CAN bus is stuck dominant state for $t > t_{BUSDOM}$. If a CANDOM condition exists the nFAULT pin is driven low upon entering silent mode from normal mode. The CANDOM flag is cleared on the next dominant-to-recessive transition on RXD or upon a transition into normal, standby, go-to-sleep, or sleep modes.

7.3.8 Local Faults

Local faults are detected in both normal mode and silent mode, but are only indicated via the nFAULT pin when the TCAN1473-Q1 transitions from normal mode to silent mode. All other mode transitions clear the local fault flag indicators.

7.3.8.1 TXD Dominant Timeout (TXD DTO)

While the CAN driver is in active mode a TXD dominant state timeout circuit prevents the local node from blocking network communication in event of a hardware or software failure where TXD is held dominant longer than the timeout period, $t > t_{TXDDTO}$. The TXD dominant state timeout circuit is triggered by a falling edge on the TXD pin. If no rising edge is seen before on TXD before $t > t_{TXDDTO}$ than the CAN driver is disabled releasing the bus lines to the recessive level. This keeps the bus free for communication between other nodes on the network.

The CAN driver will be activated again on the next dominant-to-recessive transition on the TXD pin. During a *TXDDTO* fault the high-speed receiver remains active and the RXD output pin will mirror the CAN bus.

TCAN1473-Q1

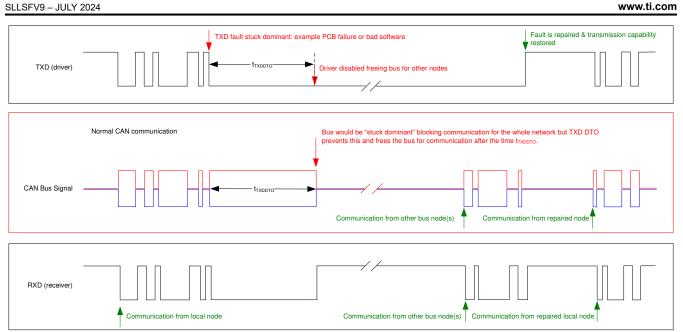


Figure 7-5. Timing Diagram for TXD DTO

The minimum dominant TXD time allowed by the dominant state timeout circuit limits the minimum possible transmitted data rate of the transceiver. The CAN protocol allows a maximum of eleven successive dominant bits to be transmitted in the worst case, where five successive dominant bits are followed immediately by an error frame. The minimum transmitted data rate may be calculated using the minimum t_{TXDDTO} time in Equation 1.

Minimum Data Rate = 11 bits / t_{TXDDTO} = 11 bits / 1.2ms = 9.2kbps (1)

7.3.8.2 Thermal Shutdown (TSD)

If the junction temperature of the TCAN1473-Q1 exceeds the thermal shutdown threshold the device turns off the CAN driver circuits thus blocking the TXD to bus transmission path. The CAN bus terminals are biased to recessive level during a *TSD* fault and the receiver to RXD path remains operational. The *TSD* fault condition is cleared when the junction temperature, T_J , of the device drops below the thermal shutdown release temperature, T_{SDF} , of the device. If the fault condition that caused the *TSD* fault is still present, the temperature may rise again and the device will enter thermal shutdown again. Prolonged operation with *TSD* fault conditions may affect device reliability. The TSD circuit includes hysteresis to avoid any oscillation of the driver output. During the fault the *TSD* fault condition is indicated to the CAN FD controller via the nFAULT terminal.

7.3.8.3 Undervoltage Lockout (UVLO)

The supply terminals, V_{SUP} , V_{IO} and V_{CC} , are monitored for undervoltage events. If an undervoltage event occurs the TCAN1473-Q1 enters a protected state where the bus pins present no load to the CAN bus. This protects the CAN bus and system from unwanted glitches and excessive current draw that could impact communication between other CAN nodes on the CAN bus.

If an undervoltage event occurs on V_{SUP} in any mode, the TCAN1473-Q1 CAN transceiver enters the CAN off state.

If an undervoltage event occurs on V_{CC}, the TCAN1473-Q1 remains in normal or silent mode but the CAN transceiver changes to the CAN autonomous active state. During a UV_{CC} event, RXD remains high as long as V_{IO} is present and the wake-up circuitry is inactive. See Figure 7-11. If the undervoltage event persists longer than t_{UV} , the TCAN1473-Q1 transitions to sleep mode.

If an undervoltage event occurs on the V_{IO} , the TCAN1473-Q1 transitions to standby mode. If the undervoltage event persists longer than t_{UV} , the TCAN1473-Q1 transitions to sleep mode.

TRUMENTS



Once an undervoltage condition is cleared and the supplies have returned to valid levels, the device typically needs 200µs to transition to normal operation.

7.3.8.4 Unpowered Devices

The device is designed to be a passive or no load to the CAN bus if the device is unpowered. The CANH and CANL pins have low leakage currents when the device is unpowered, thus, presenting no load to the bus. This is critical if some nodes of the network are unpowered while the rest of the of network remains in operation.

The logic terminals also have low leakage currents when the device is unpowered, so the terminals do not load down other circuits which may remain powered.

7.3.8.5 Floating Terminals

The TCAN1473-Q1 has internal pull-ups and pull-downs on critical pins to make sure a known operating behavior if the pins are left floating. See Table 7-3 for the pin fail-safe biasing protection description.

PIN	FAIL-SAFE PROTECTION	Recessive level Weak pull-up to V _{IO}										
TXD	Recessive level		Weak pull-up to V _{IO}									
EN	Low-power mode	60kΩ	Weak pull-down to GND									
nSTB	Low-power mode		Weak pull-down to GND									

Table 7-3. Pin Fail-safe Biasing

This internal bias should not be relied upon by design but rather a fail-safe option. Special care needs to be taken when the transceiver is used with a CAN FD controller that has open-drain outputs. The TCAN1473-Q1 implements a weak internal pull-up resistor on the TXD pin. The bit timing requirements for CAN FD data rates require special consideration and the pull-up strength should be considered carefully when using open-drain outputs. An adequate external pull-up resistor must be used to make sure the TXD output of the CAN FD controller maintains proper bit timing input to the CAN device.

7.3.8.6 CAN Bus Short-Circuit Current Limiting

The TCAN1473-Q1 has several protection features that limit the short-circuit current when a CAN bus line is shorted. The features include CAN driver current limiting in the dominant and recessive states, and TXD dominant state timeout which prevents permanently having the higher short-circuit current of a dominant state in a system fault.

During CAN communication, the bus switches between the dominant and recessive states. Thus, the shortcircuit current may be viewed either as the current during each bus state or as an average current. The average short-circuit current can be used when considering system power for the termination resistors and common-mode choke. The percentage of time that the driver can be dominant is limited by the TXD dominant state timeout and the CAN protocol which has forced state changes and recessive bits such as bit stuffing, control fields, and interframe spacing. These make sure there is a minimum recessive time on the bus even if the data field contains a high percentage of dominant bits.

The short-circuit current of the bus depends on the ratio of recessive to dominant bits and the respective short-circuit currents. The average short-circuit current may be calculated using Equation 2.

 $I_{OS(AVG)} = \% Transmit \times [(\% REC_Bits \times I_{OS(SS)_REC}) + (\% DOM_Bits \times I_{OS(SS)_DOM})] + [\% Receive \times I_{OS(SS)_REC}]$ (2)

Where:

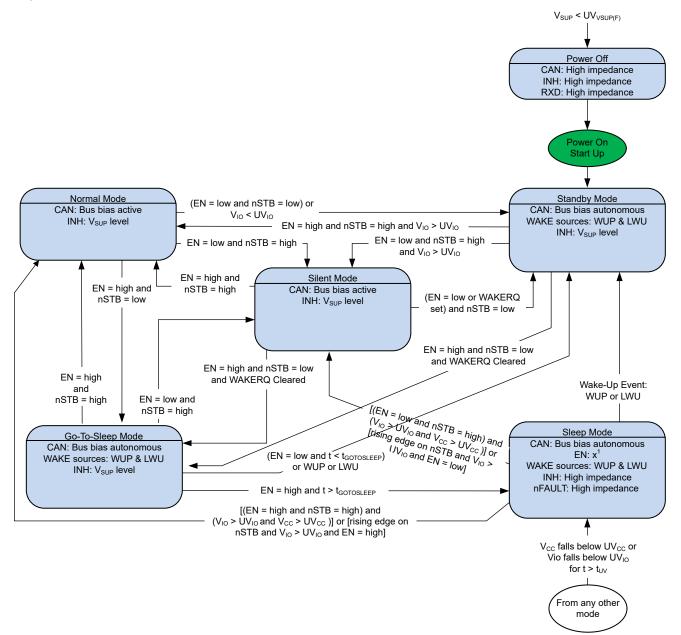
- I_{OS(AVG)} is the average short-circuit current
- %Transmit is the percentage the node is transmitting CAN messages
- %Receive is the percentage the node is receiving CAN messages
- %REC_Bits is the percentage of recessive bits in the transmitted CAN messages
- %DOM_Bits is the percentage of dominant bits in the transmitted CAN messages
- I_{OS(SS) REC} is the recessive steady state short-circuit current
- I_{OS(SS) DOM} is the dominant steady state short-circuit current



The short-circuit current and possible fault cases of the network should be taken into consideration when sizing the power ratings of the termination resistance and other network components.

7.4 Device Functional Modes

The TCAN1473-Q1 has six operating modes: normal, standby, silent, go-to-sleep, sleep, and off mode. Operating mode selection is controlled using the nSTB pin and EN pin in conjunction with supply conditions, temperature conditions, and wake events.



1. The enable pin can be in a logical high or low state while in sleep mode but since it has an internal pull-down, the lowest possible power consumption occurs when the pin is left either floating or pulled low externally.

Figure 7-6. TCAN1473-Q1 State Machine

Table 7-4. TCAN1473-Q1 Mode Overview

MODE	V_{CC} and V_{IO}	V _{SUP}	EN	nSTB	WAKERQ FLAG	DRIVER	RECEIVER	RXD	INH
Normal	$> \mathrm{UV}_\mathrm{CC}$ and $> \mathrm{UV}_\mathrm{IO}$	$> UV_{SUP}$	High	High	Х	Enabled	Enabled	Mirrors bus state	On



Table 7-4. TCAN1473-QT Mode Overview (continued)											
MODE	V_{CC} and V_{IO}	V _{SUP}	EN	nSTB	WAKERQ FLAG	DRIVER	RECEIVER	RXD	INH		
Silent	$> \rm UV_{\rm CC}$ and $> \rm UV_{\rm IO}$	> UV _{SUP}	Low	High	Х	Disabled	Enabled	Mirrors bus state	On		
	> UV _{CC} and> UV _{IO}	> UV _{SUP}	High	Low	Set	Disabled	Low power bus monitor enabled	Low signals wake-up	On		
Standby	> UV _{CC} and > UV _{IO}	> UV _{SUP}	Low	Low	Х	Disabled	Low power bus monitor enabled	Low signals wake-up	On		
	> UV _{CC} and < UV _{IO}	> UV _{SUP}	Low	Low	Х	Disabled	Low power bus monitor enabled	High impedance	On		
Go-to-sleep ⁽¹⁾	> UV _{CC} and $>$ UV _{IO}	> UV _{SUP}	High	Low	Cleared	Disabled	Low power bus monitor enabled	High or high impedance (no V _{IO})	On ⁽²⁾		
Sleep ⁽³⁾	$> \mathrm{UV}_\mathrm{CC}$ and $> \mathrm{UV}_\mathrm{IO}$	> UV _{SUP}	High	Low	Cleared	Disabled	Low power bus monitor enabled	High or high impedance (no V _{IO})	High Impedance		
Clock	< UV _{CC} or <uv<sub>IO</uv<sub>	> UV _{SUP}	x	х	Х	Disabled	Low power bus monitor enabled	High or high impedance (no V _{IO})	High impedance		
Protected	х	< UV _{SUP}	x	х	Х	Disabled	Disabled	High impedance	High impedance		

Table 7-4. TCAN1473-Q1 Mode Overview (continued)

(1) Go-to-sleep: Transitional mode for EN = H, nSTB = L until $t_{GOTOSLEEP}$ timer has expired.

(2) The INH pin transitions to high impedance after the t_{GOTOSLEEP} timer has expired.

(3) Mode change from go-to-sleep mode to sleep mode once t_{GOTOSLEEP} timer has expired.

7.4.1 Operating Mode Description

7.4.1.1 Normal Mode

This is the normal operating mode of the device. The CAN driver and receiver are fully operational and CAN communication is bi-directional. The driver is translating a digital input on TXD to a differential output on CANH and CANL. The receiver is translating the differential signal from CANH and CANL to a digital output on RXD.

Entering normal mode clears both the WAKERQ and the PWRON flags.

7.4.1.2 Silent Mode

Silent mode is commonly referred to as listen only and receive only mode. In this mode, the CAN driver is disabled but the receiver is fully operational and CAN communication is unidirectional into the device. The receiver is translating the differential signal from CANH and CANL to a digital output on the RXD terminal.

In silent mode, PWRON and Local Failure flags are indicated on the nFAULT pin.

7.4.1.3 Standby Mode

Standby mode is a low-power mode where the driver and receiver are disabled, reducing current consumption. However, this is not the lowest power mode of the device since the INH terminal is on, allowing the rest of the system to resume normal operation.

During standby mode, a wake-up request (*WAKERQ*) is indicated by the RXD terminal being low. The wake-up source is identified via the nFAULT pin after the device is returned to normal mode.

7.4.1.4 Go-To-Sleep Mode

Go-to-sleep mode is the transitional mode of the device from any state to sleep. In this state the driver and receiver are disabled, reducing the current consumption. The INH pin is active to supply an enable to the V_{IO} controller which allows the rest of the system to operate normally. If the device is held in this state for t \geq t_{GOTOSLEEP} the device transitions to sleep mode and the INH turns off transitioning to the high impedance state.

If any wake-up events persist, the TCAN1473-Q1 remains in standby mode until the device is switched into normal mode to clear the pending wake-up events.

7.4.1.5 Sleep Mode

Sleep mode is the lowest power mode of the TCAN1473-Q1. In sleep mode, the CAN transmitter and the main receiver are switched off and the transceiver cannot send or receive data. The low power receiver is able to monitor the bus for any activity that validates the wake-up pattern (WUP) requirements, and the WAKE monitoring circuit monitors for state changes on the WAKE terminal for a local wake-up (LWU) event. I_{SUP} current is reduced to the minimum level when the CAN transceiver is in CAN autonomous inactive state. The

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INH pin is switched off in sleep mode causing any system power supplies controlled by INH to be switched off thus reducing system power consumption.

Sleep mode is exited:

- If a valid wake-up pattern (WUP) is received via the CAN bus pins
- On a local WAKE (LWU) event
- nSTB is high and VCC > UV_{CC} and VIO > UV_{IO} (the device enters Normal or Silent mode depending upon the logic level on the EN pin.

7.4.1.5.1 Remote Wake Request via Wake-Up Pattern (WUP)

The TCAN1473-Q1 implements a low-power wake receiver in the standby and sleep mode that uses the multiple filtered dominant wake-up pattern (WUP) defined in the ISO11898-2:2024 standard.

The wake-up pattern (WUP) consists of a filtered dominant bus, then a filtered recessive bus time followed by a second filtered dominant bus time. The first filtered dominant initiates the WUP and the bus monitor is now waiting on a filtered recessive; other bus traffic will not reset the bus monitor. Once a filtered recessive is received, the bus monitor is now waiting on a filtered dominant, and other bus traffic does not reset the bus monitor. Immediately upon receiving of the second filtered dominant, the bus monitor recognizes the WUP, and drives the RXD terminal low. If a valid V_{IO} is present, the controller is signaled for a wake-up request. If a valid V_{IO} is not present when the wake-up pattern is received, the transceiver drives the RXD output pin low once V_{IO} > UV_{IOR}.

The WUP consists of:

- A filtered dominant bus of at least t_{WK(FILTER)} followed by
- A filtered recessive bus time of at least $t_{WK(FILTER)}$ followed by
- A second filtered dominant bus time of at least t_{WK(FILTER)}

For a dominant or recessive to be considered *filtered*, the bus must be in that state for more than $t_{WK(FILTER)}$ time. Due to variability in the $t_{WK(FILTER)}$, the following scenarios are applicable. Bus state times less than the $t_{WK(FILTER)}$ minimum are never detected as part of a WUP, and no wake request is generated. Bus state times between $t_{WK(FILTER)}$ minimum and $t_{WK(FILTER)}$ maximum may be detected as part of a WUP and a wake request may be generated. Bus state times more than $t_{WK(FILTER)}$ maximum is always detected as part of a WUP, and a wake request is always generated. See Figure 7-7 for the timing diagram of the WUP.

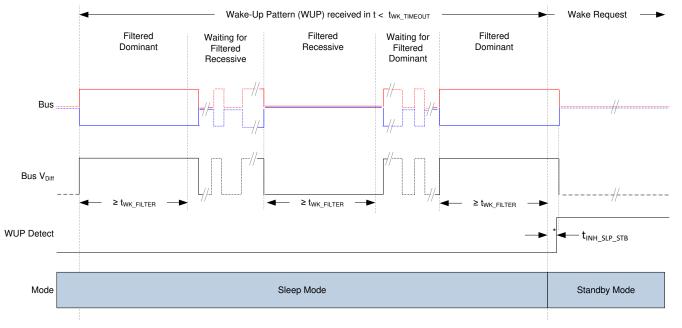
The pattern and t_{WK(FILTER)} time used for the WUP and wake request prevents noise and bus stuck dominant faults from causing false wake requests while allowing any CAN or CAN FD message to initiate a wake request.

ISO11898-2:2024 has two sets of times for a short and long wake-up filter times. The $t_{WK(FILTER)}$ timing for the TCAN1473-Q1 has been picked to be within the min and max values of both filter ranges. This timing has been chosen such that a single bit time at 500kbps, or two back to back bit times at 1Mbps triggers the filter in either bus state.

For an additional layer of robustness and to prevent false wake-ups, the transceiver implements the $t_{WK(TIMEOUT)}$ timer. For a remote wake-up event to successfully occur, the entire wake-up pattern must be received within the timeout value. If the full wake-up pattern is not received before the $t_{WK(TIMEOUT)}$ expires then the internal logic is reset and the transceiver remains in sleep mode without waking up. The full pattern must then be transmitted again within the $t_{WK(TIMEOUT)}$ window. See Figure 7-7.

A recessive bus of at least $t_{WK(FILTER)}$ must separate the next WUP pattern if the CAN bus is dominant when the $t_{WK(TIMEOUT)}$ expires.





*The RXD pin is only driven once V_{IO} is present.

Figure 7-7. Wake-Up Pattern (WUP)

7.4.1.5.2 Local Wake-Up (LWU) via WAKE Input Terminal

The WAKE terminal is a bi-directional high-voltage reverse-battery protected input which can be used for local wake-up (LWU) requests via a voltage transition. A LWU event is triggered on either a low-to-high or high-to-low transition since it has bi-directional input thresholds. The WAKE pin could be used with a switch to V_{SUP} or to ground. If the terminal is unused it should be pulled to V_{SUP} or ground to avoid unwanted parasitic wake-up events.

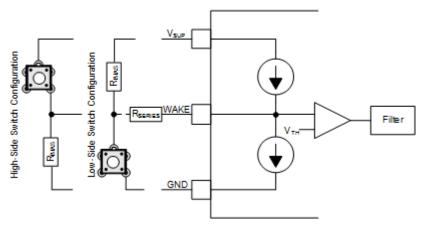


Figure 7-8. WAKE Circuit Example

Figure 7-8 shows two possible configurations for the WAKE pin, a low-side and high-side switch configuration. The objective of the series resistor, R_{SERIES}, is to protect the WAKE input of the device from over current conditions that may occur in the event of a ground shift or ground loss. The minimum value of R_{SERIES} can be calculated using the maximum supply voltage, V_{SUPMAX}, and the maximum allowable current of the WAKE pin, I_{IO(WAKE)}. R_{SERIES} is calculated using:

 $R_{SERIES} = V_{SUPMAX} / I_{IO(WAKE)}$

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With absolute maximum voltage, V_{SUPMAX} , of 45V and maximum allowable $I_{IO(WAKE)}$ of 3mA, the minimum required R_{SERIES} value is 15k Ω .

The R_{BIAS} resistor is used to set the static voltage level of the WAKE input when the switch is released. When the switch is in use in a high-side switch configuration, the R_{BIAS} resistor in combination with the R_{SERIES} resistor sets the WAKE pin voltage above the V_{IH} threshold. The maximum value of R_{BIAS} can be calculated using the maximum supply voltage, V_{SUPMAX}, the maximum WAKE threshold voltage V_{IH}, the maximum WAKE input current I_{IH} and the series resistor value R_{SERIES}. R_{BIAS} is calculated using:

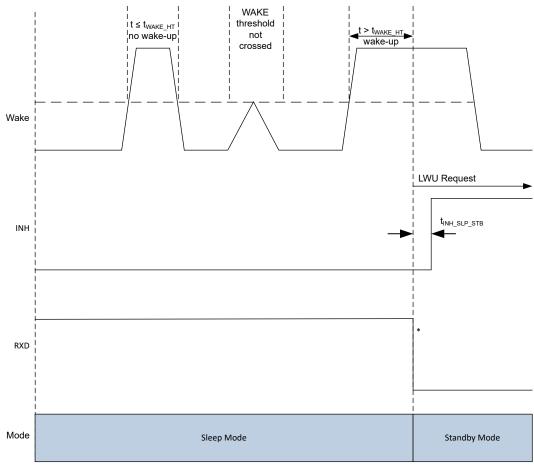
 $R_{BIAS} < ((V_{SUPMAX} - V_{IH}) / I_{IH}) - R_{SERIES}$

(4)

With V_{SUPMAX} of 45V, V_{IH} of 44V at I_{IH} of 3µA, the R_{BIAS} resistor value must be less than 330k Ω . It is recommended to use R_{Series} less than 50k Ω to provide better margin for the WAKE pin voltage to rise above V_{IH} when the switch is released.

The LWU circuitry is active in sleep mode.

The WAKE circuitry is switched off in normal mode.



* RXD is driven with valid $V_{\rm IO}$





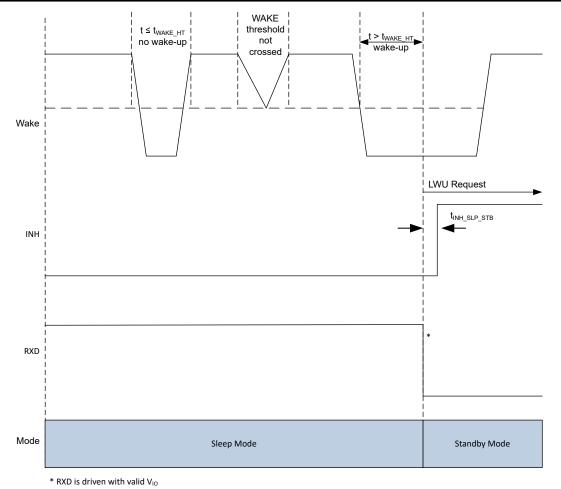


Figure 7-10. LWU Request Falling Edge

7.4.2 CAN Transceiver

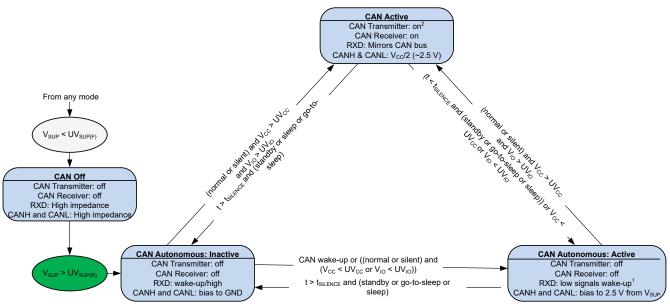
7.4.2.1 CAN Transceiver Operation

The TCAN1473-Q1 supports the ISO 11898-2:2024 CAN physical layer standard autonomous bus biasing scheme. Autonomous bus biasing enables the transceiver to switch between CAN active, CAN autonomous active, and CAN autonomous inactive which helps to reduce RF emissions.

7.4.2.1.1 CAN Transceiver Modes

The TCAN1473-Q1 CAN transceiver has four modes of operation; CAN off, CAN autonomous active, CAN autonomous inactive and CAN active.





- 1. Wake-up is inactive in normal or silent mode.
- 2. CAN transmitter is off in silent mode.

Figure 7-11. TCAN1473-Q1 CAN Transceiver State Machine

7.4.2.1.1.1 CAN Off Mode

In CAN off mode the CAN transceiver is switched off and the CAN bus lines are truly floating. In this mode the device presents no load to the CAN bus while preventing reverse currents from flowing into the device if the battery or ground connection is lost.

The CAN off state is entered if:

V_{SUP} < UV_{SUPF}

The CAN transceiver switches between the CAN off state and CAN autonomous inactive mode if:

• $V_{SUP} > UV_{SUPR}$

7.4.2.1.1.2 CAN Autonomous: Inactive and Active

When the CAN transceiver is in standby, go-to-sleep or sleep mode, the bias circuit can be in either the CAN autonomous inactive or CAN autonomous active state. In the autonomous inactive state, the CAN pins are biased to GND. When a remote wake-up (WUP) event occurs, the CAN bus is biased to 2.5V and the CAN transceiver enters the CAN autonomous active state. If the controller does not transition the transceiver into normal mode before the $t_{SILENCE}$ timer expires, the CAN transceiver enters the CAN autonomous inactive state.

The CAN transceiver switches to the CAN autonomous mode if any of the following conditions are met:

- The operating mode changes from CAN off mode to CAN autonomous inactive
- The operating mode changes from normal or silent mode to standby, go-to-sleep, or sleep mode:
 - If the bus was inactive for t < t_{SILENCE} before the mode change, the transceiver enters autonomous active state
 - If the bus was inactive for t > t_{SILENCE} before the mode change, the transceiver enters autonomous inactive state
- $V_{CC} < UV_{CC(F)}$
- $V_{IO} < UV_{IO(F)}$

The CAN transceiver switches from the CAN autonomous inactive mode to the CAN autonomous active mode if:

- A remote wake-up event occurs
- The transceiver transitions to normal or silent mode and $V_{CC} < UV_{CC(F)}$ or $V_{IO} < UV_{IO(F)}$

The CAN transceiver switches from the CAN autonomous active mode to the CAN autonomous inactive mode if:



The transceiver is in standby, go-to-sleep, or sleep mode and t > t_{SILENCE}

7.4.2.1.1.3 CAN Active

When the transceiver is in normal or silent mode, the CAN transceiver is in active mode. In normal mode, the CAN driver and receiver are fully operational and CAN communication is bi-directional. In silent mode, the CAN driver is off but the CAN receiver is fully operational. The CAN bias voltage in CAN active mode is derived from V_{CC} and is held at $V_{CC}/2$

The CAN transceiver switches from the CAN autonomous inactive or CAN autonomous active modes to the CAN active mode if:

• The transceiver transitions to normal mode and $V_{CC} > UV_{CC(R)}$, $V_{IO} > UV_{IO(R)}$

The CAN transceiver switches from the CAN active mode to the CAN autonomous inactive mode if:

The transceiver switches to standby, go-to-sleep, or sleep modes and t > t_{SILENCE}

The CAN transceiver switches from the CAN active mode to the CAN autonomous active mode if:

- The transceiver switches to standby, go-to-sleep, or sleep modes and t < t_{SILENCE}
- $V_{CC} < UV_{CC(F)}$
- V_{IO} < UV_{IO(F)}

7.4.2.1.2 Driver and Receiver Function Tables

DEVICE MODE	TXD INPUTS ⁽¹⁾	BUS OUTPUTS		DRIVEN BUS STATE ⁽²⁾
		CANH	CANL	DRIVEN BUS STATE
Normal	Low	High	Low	Dominant
	High or Open	High impedance	High impedance	V _{CC} /2
Silent	х	High impedance	High impedance	V _{CC} /2
Standby	х	High impedance	High impedance	Autonomous biasing
Sleep	x	High impedance	High impedance	Autonomous biasing

 Table 7-5. Driver Function Table

(1) x = irrelevant

(2) For bus states and typical bus voltages see Figure 7-12

 Table 7-6. Receiver Function Table

DEVICE MODE	$\begin{array}{l} \text{CAN DIFFERENTIAL INPUTS} \\ \text{V}_{\text{ID}} = \text{V}_{\text{CANH}} - \text{V}_{\text{CANL}} \end{array}$	BUS STATE	RXD TERMINAL	
Normal / Silent	$V_{ID} \ge 0.9 V$	Dominant	Low	
	0.5 V < V _{ID} < 0.9 V	Indeterminate	Indeterminate	
	V _{ID} ≤ 0.5 V	Recessive	High	
	Open (V _{ID} ≈ 0 V)	Open	High	
Standby	V _{ID} ≥ 1.15 V	Dominant		
	0.4 V < V _{ID} < 1.15 V	Indeterminate	High Low if wake-up event persists	
	V _{ID} ≤ 0.4	Recessive		
	Open (V _{ID} ≈ 0 V)	Open		
Sleep / Go-to- sleep ⁽¹⁾	V _{ID} ≥ 1.15 V	Dominant		
	0.4 V < V _{ID} < 1.15 V	Indeterminate	High Tri-state if V _{IO} or V _{SUP} are not present	
	V _{ID} ≤ 0.4 V	Recessive		
	Open (V _{ID} ≈ 0 V)	Open		

(1) Low power wake-up receiver is active



7.4.2.1.3 CAN Bus States

The CAN bus has two logical states during operation: recessive and dominant. See Figure 7-12.

A dominant bus state occurs when the bus is driven differentially and corresponds to a logic low on the TXD and RXD pins. A recessive bus state occurs when the bus is biased to one half of the CAN transceiver supply voltage via the high resistance internal input resistors (R_{IN}) of the receiver and corresponds to a logic high on the TXD and RXD pins.

A dominant state overwrites the recessive state during arbitration. Multiple CAN nodes may be transmitting a dominant bit at the same time during arbitration when the differential voltage of the CAN bus is greater than the differential voltage of a single CAN driver. The TCAN1473-Q1 CAN transceiver implements low-power standby and sleep modes which enable a third bus state where, if the CAN bus is inactive for t > t_{SILENCE}. The bus pins are biased to ground via the high-resistance internal resistors of the receiver.

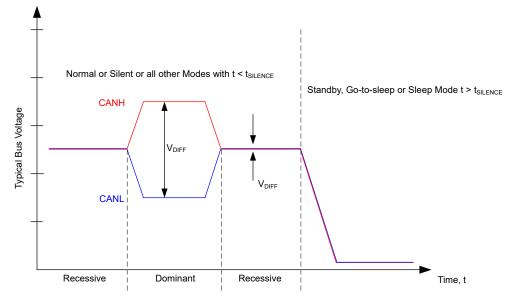


Figure 7-12. Bus States



8 Application Information Disclaimer

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The TCAN1473-Q1 transceiver is typically used in applications with a host microprocessor or FPGA that includes the data link layer portion of the CAN protocol. These types of applications usually also include power management technology that allows for power to be gated to the application via an enable (EN) or inhibit (INH) pin. A single 5V regulator can be used to drive both V_{CC} and V_{IO} , or independent 5V and 3.3V regulators can be used to drive V_{CC} and V_{IO} separately as shown in Figure 8-1. The bus termination is shown for illustrative purposes.

The TCAN1473-Q1 features an INH_MASK feature. The INH_MASK input pin can be used to disable and enable the INH function as long as the INH is not controlling the power supply to the transceiver or the controller behind the transceiver. This feature can be used to control the power supply to any power-intensive system blocks to avoid powering up the system blocks from low-power mode due to spurious wake-up events which saves power. See Figure 8-1 for an example application schematic.

8.1.1 Typical Application

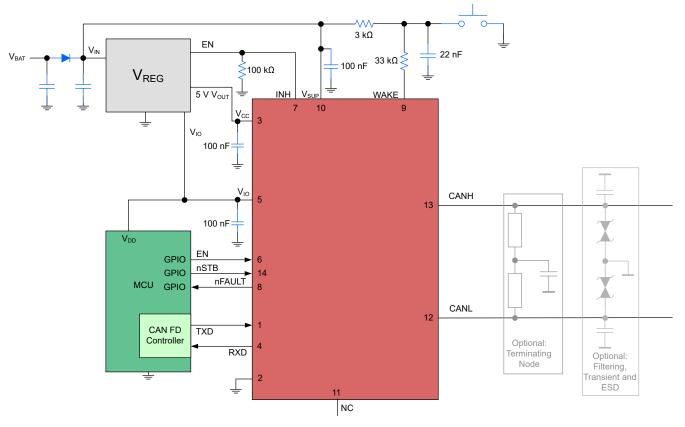


Figure 8-1. Typical Application



8.1.2 Design Requirements

8.1.2.1 Bus Loading, Length and Number of Nodes

A typical CAN application may have a maximum bus length of 40 meters and maximum stub length of 0.3m. However, with careful design, users can have longer cables, longer stub lengths, and many more nodes to a bus. A high number of nodes requires a transceiver with high input impedance such as the TCAN1473-Q1.

Many CAN organizations and standards have scaled the use of CAN for applications outside the original ISO11898-2:2024 standard. They made system level trade off decisions for data rate, cable length, and parasitic loading of the bus. Examples of these CAN systems level specifications are ARINC825, CANopen, DeviceNet, SAEJ2284, SAEJ1939, and NMEA200.

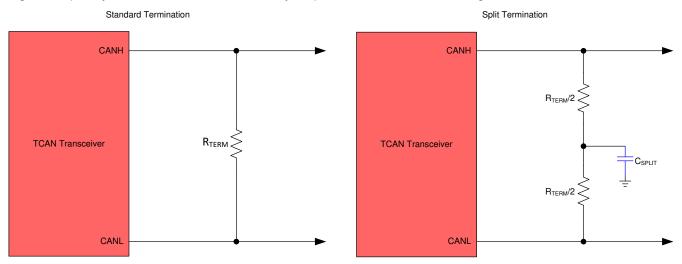
A CAN network system design is a series of tradeoffs. In the ISO 11898-2:2024 specification the differential output driver is specified with a bus load that can range from 50Ω to 65Ω where the differential output must be greater than 1.5V. The TCAN1473-Q1 is specified to meet the 1.5V requirement down to 50Ω and is specified to meet 1.4-V differential output at 45Ω bus load. The differential input resistance, R_{ID}, of the TCAN1473-Q1 is a minimum of $50k\Omega$. If 100 TCAN1473-Q1 transceivers are in parallel on a bus, this is equivalent to a 500Ω differential load in parallel with the nominal 60Ω bus termination which gives a total bus load of approximately 54Ω . Therefore, the TCAN1473-Q1 theoretically supports over 100 transceivers on a single bus segment. However, for CAN network design margin must be given for signal loss across the system and cabling, parasitic loadings, timing, network imbalances, ground offsets and signal integrity thus a practical maximum number of nodes is often lower. Bus length may also be extended beyond 40 meters by careful system design and data rate tradeoffs. For example, CANopen network design guidelines allow the network to be up to 1km with changes in the termination resistance, cabling, less than 64 nodes and significantly lowered data rate.

This flexibility in CAN network design is one of the key strengths allowing for these system level network extensions and additional standards to build on the original ISO11898-2 CAN standard. However, when using this flexibility, the CAN network system designer must take the responsibility of good network design for a robust network operation.

8.1.3 Detailed Design Procedure

8.1.3.1 CAN Termination

Termination may be a single 120Ω resistor at each end of the bus, either on the cable or in a terminating node. If filtering and stabilization of the common-mode voltage of the bus is desired then split termination may be used, see Figure 8-2. Split termination improves the electromagnetic emissions behavior of the network by filtering higher-frequency common-mode noise that may be present on the differential signal lines.







8.1.4 Application Curves

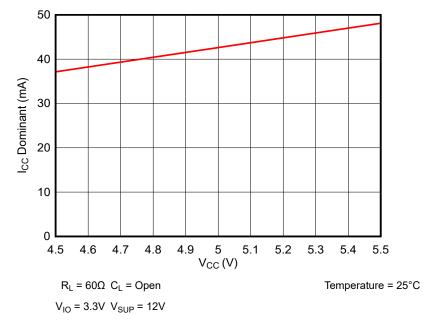


Figure 8-3. I_{CC} Dominant over I_{CC} Supply Voltage

8.2 Power Supply Recommendations

The TCAN1473-Q1 is designed to operate off of three supply rails; V_{SUP} , V_{CC} , and V_{IO} . V_{SUP} is a high-voltage supply pin designed to connect to the V_{BAT} rail, V_{CC} is a low-voltage supply pin with an input voltage range from 4.5V to 5.5V that supports the CAN transceiver and V_{IO} is a low-voltage supply pin with an input voltage range from 1.7V to 5.5V that provides the I/O voltage to match the system controller. For a reliable operation, a 100nF decoupling capacitor should be placed as close to the supply pins as possible. This helps to reduce supply voltage ripple present on the output of switched-mode power supplies, and also helps to compensate for the resistance and inductance of the PCB power planes.

8.3 Layout

Robust and reliable CAN node design may require special layout techniques depending on the application and automotive design requirements. Since transient disturbances have high frequency content and a wide bandwidth, high-frequency layout techniques should be applied during PCB design.

8.3.1 Layout Guidelines

The layout example provides information on components around the device. Place the protection and filtering circuitry as close to the bus connector, J1, to prevent transients, ESD and noise from propagating onto the board. Transient voltage suppression (TVS) device can be added for extra protection, shown as D1. The production solution can be either a bi-directional TVS diode or varistor with ratings matching the application requirements. This example also shows optional bus filter capacitors C6 and C7. A series common-mode choke (CMC) is placed on the CANH and CANL lines between the device and connector J1.

Design the bus protection components in the direction of the signal path. Do not force the transient current to divert from the signal path to reach the protection device. Use supply and ground planes to provide low inductance. Note that high-frequency currents follow the path of least impedance and not the path of least resistance. Use at least two vias for supply and ground connections of bypass capacitors and protection devices to minimize trace and via inductance.

- Bypass and bulk capacitors should be placed as close as possible to the supply terminals of transceiver, examples are C1 on V_{CC}, C2 on V_{IO}, and C3 and C4 on the V_{SUP} supply.
- V_{IO} pin of the transceiver is connected to the microcontroller IO supply voltage 'µC V'.



- Bus termination: this layout example shows split termination. This is where the termination is split into two resistors, R3 and R4, with the center or split tap of the termination connected to ground via capacitor C5. Split termination provides common-mode filtering for the bus. When bus termination is placed on the board instead of directly on the bus, additional care must be taken to make sure the terminating node is not removed from the bus thus also removing the termination.
- INH, pin 7, can have a $100k\Omega$ resistor (R1) to ground.
- WAKE, pin 9, can recognize either a rising or a falling edge of a wake signal and is usually connected to an external switch. It should be configured as shown with C8 which is a 22nF capacitor to GND where R5 is 33kΩ and R6 is 3kΩ.
- INH_MASK, pin 11, can be left floating or connected to GND when INH_MASK function is not used. Do not connect to V_{IO} .

8.3.2 Layout Example

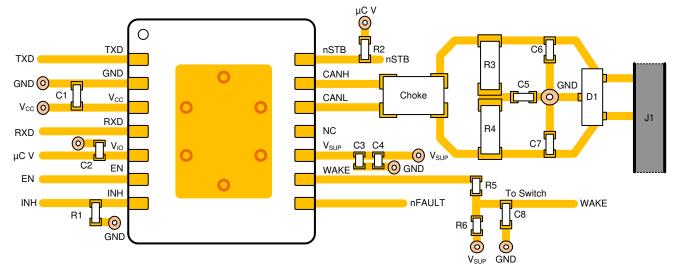


Figure 8-4. Example Layout



9 Device and Documentation Support

9.1 Documentation Support

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.4 Trademarks

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9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
July 2024	*	Initial Release

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

11.1 Package Option Addendum



11.1.1 Packaging Information

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish ⁽⁴⁾	MSL Peak Temp ⁽³⁾	Op Temp (°C)	Device Marking ^{(5) (6)}
TCAN1473DYYRQ1	PREVIEW	SOT-23- THN	DYY	14	3000	RoHS & Green	NIPDAU	Call TI	-40 to 125	TCAN1473
TCAN1473DRQ1	PREVIEW	SOIC	D	14	2500	RoHS & Green	NIPDAU	Call TI	-40 to 125	TCAN1473
TCAN1473DMTRQ1	PREVIEW	VSON	DMT	14	3000	RoHS & Green	NIPDAU	Call TI	-40 to 125	TCAN1473
PTCAN1473DYYRQ1	ACTIVE	SOT-23- THN	DYY	14	3000	RoHS & Green	NIPDAU	Call TI	-40 to 125	PTCAN1473
PTCAN1473DRQ1	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Call TI	-40 to 125	PTCAN1473
PTCAN1473DMTRQ1	ACTIVE	VSON	DMT	14	3000	RoHS & Green	NIPDAU	Call TI	-40 to 125	PTCAN1473

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PRE_PROD Unannounced device, not in production, not available for mass market, nor on the web, samples not available.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

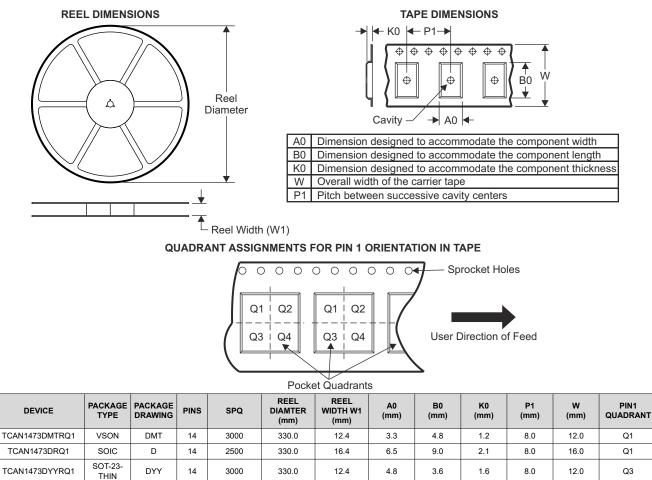
- (3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.
- (5) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device
- (6) Multiple Device markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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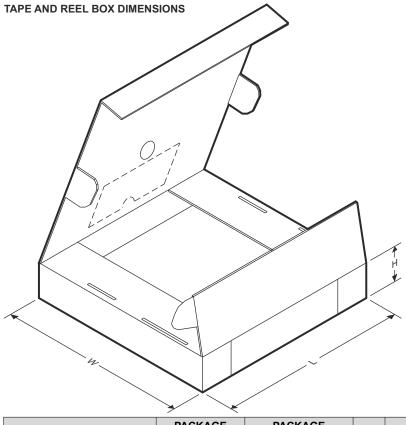


11.1.2 Tape and Reel Information



TCAN1473-Q1 SLLSFV9 – JULY 2024





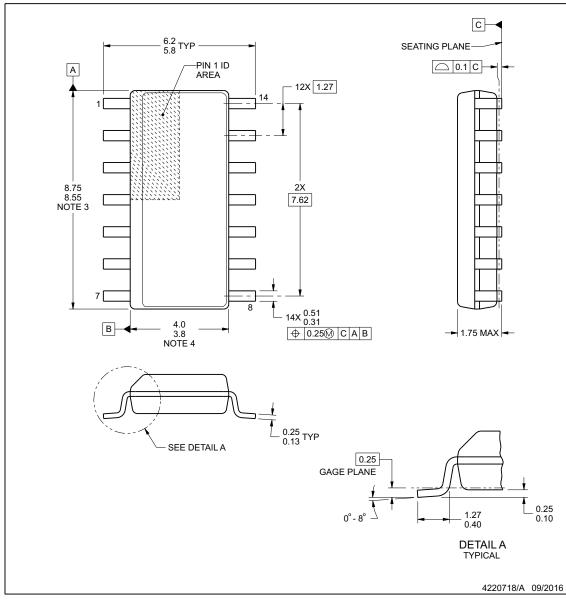
DEVICE	PACKAGE TYPE	PACKAGE DRAWING	PINS	SPQ	LENGTH (mm)	WIDTH (mm)	HEIGHT (mm)
TCAN1473DMTRQ1	VSON	DMT	14	3000	367.0	367.0	35.0
TCAN1473DRQ1	SOIC	D	14	2500	356.0	356.0	35.0
TCAN1473DYYRQ1	SOT-23-THIN	DYY	14	3000	336.6	336.6	31.8



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.

3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not

exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.

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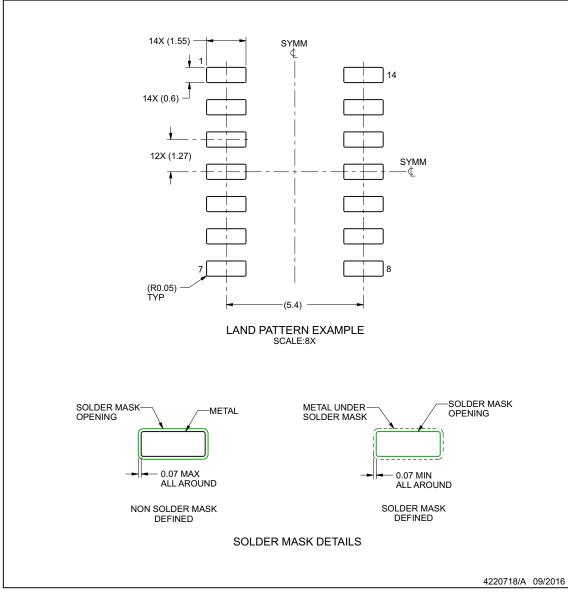


EXAMPLE BOARD LAYOUT

D0014A

SOIC - 1.75 mm max height





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

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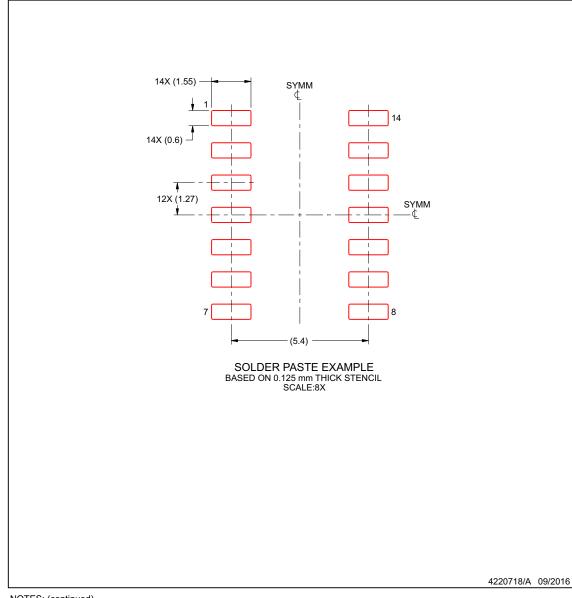


EXAMPLE STENCIL DESIGN

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.9. Board assembly site may have different recommendations for stencil design.

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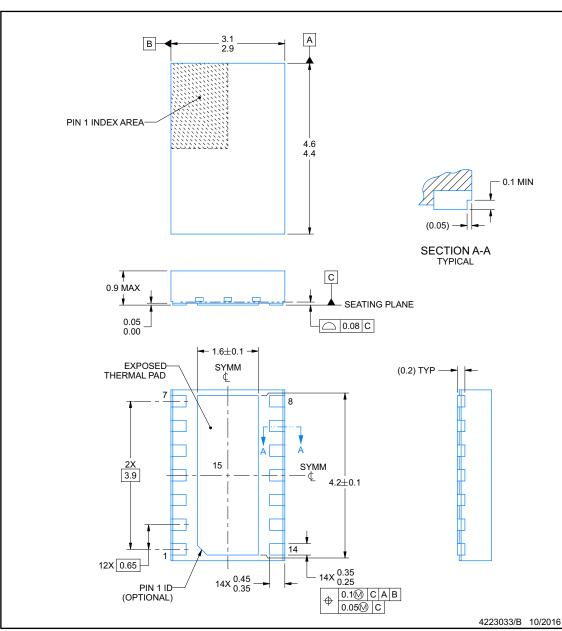
DMT0014A



PACKAGE OUTLINE

VSON - 0.9 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



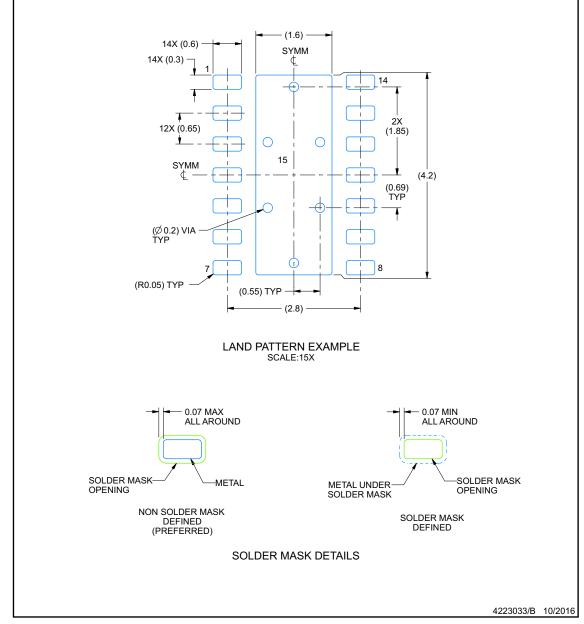


DMT0014A

EXAMPLE BOARD LAYOUT

VSON - 0.9 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

5. Vitas are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



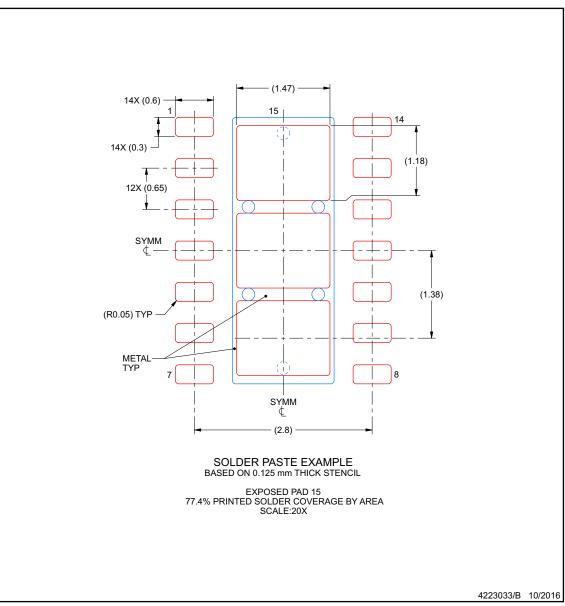


EXAMPLE STENCIL DESIGN

DMT0014A

VSON - 0.9 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

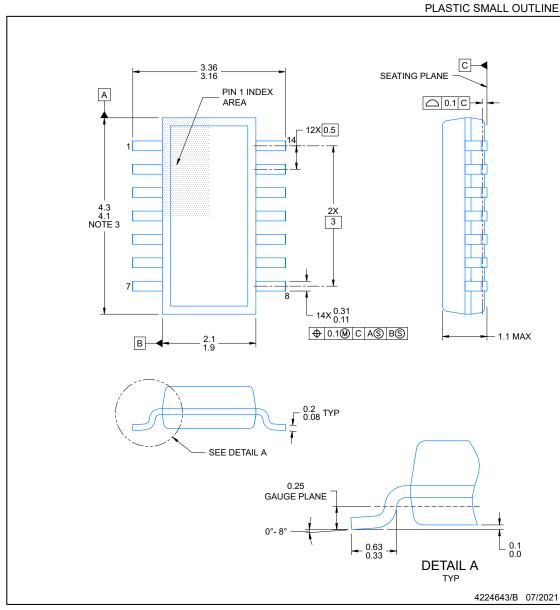
6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





PACKAGE OUTLINE

SOT-23-THIN - 1.1 mm max height



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- 5. Reference JEDEC Registration MO-345, Variation AB



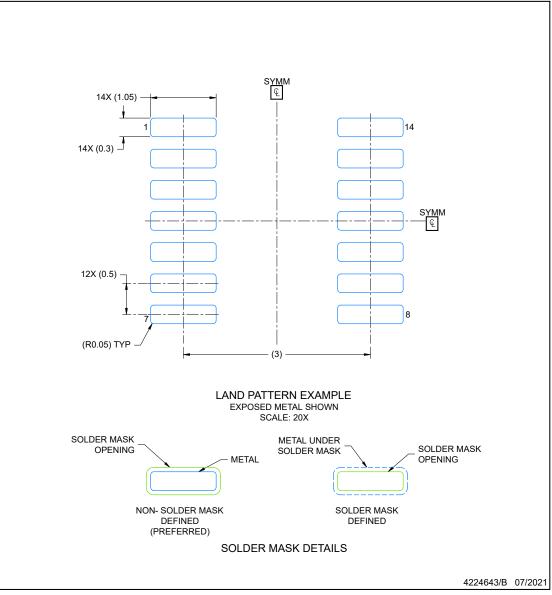


EXAMPLE BOARD LAYOUT

SOT-23-THIN - 1.1 mm max height



PLASTIC SMALL OUTLINE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



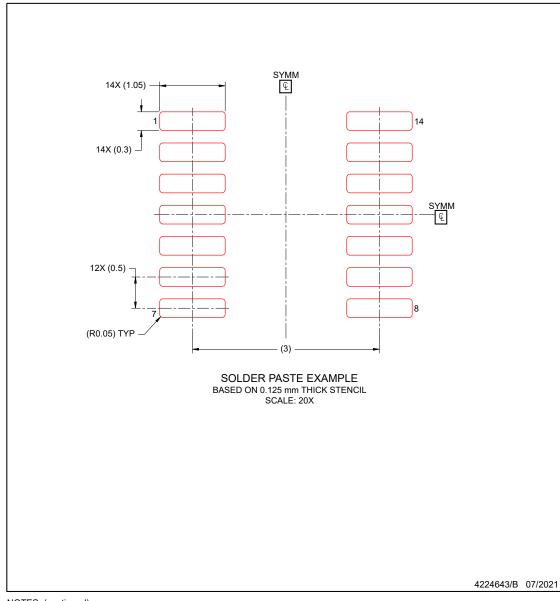


EXAMPLE STENCIL DESIGN

SOT-23-THIN - 1.1 mm max height



PLASTIC SMALL OUTLINE



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.





PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	. ,		_			.,	(6)	(<i>)</i>			
PTCAN1473DMTRQ1	ACTIVE	VSON	DMT	14	3000	TBD	Call TI	Call TI	-40 to 150		Samples
PTCAN1473DRQ1	ACTIVE	SOIC	D	14	3000	TBD	Call TI	Call TI	-40 to 150		Samples
PTCAN1473DYYRQ1	ACTIVE	SOT-23-THIN	DYY	14	3000	TBD	Call TI	Call TI	-40 to 150		Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.



EXAMPLE BOARD LAYOUT

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



EXAMPLE STENCIL DESIGN

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



DMT 14

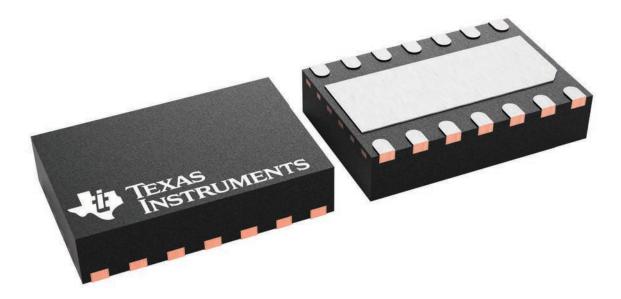
3 x 4.5, 0.65 mm pitch

GENERIC PACKAGE VIEW

VSON - 0.9 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

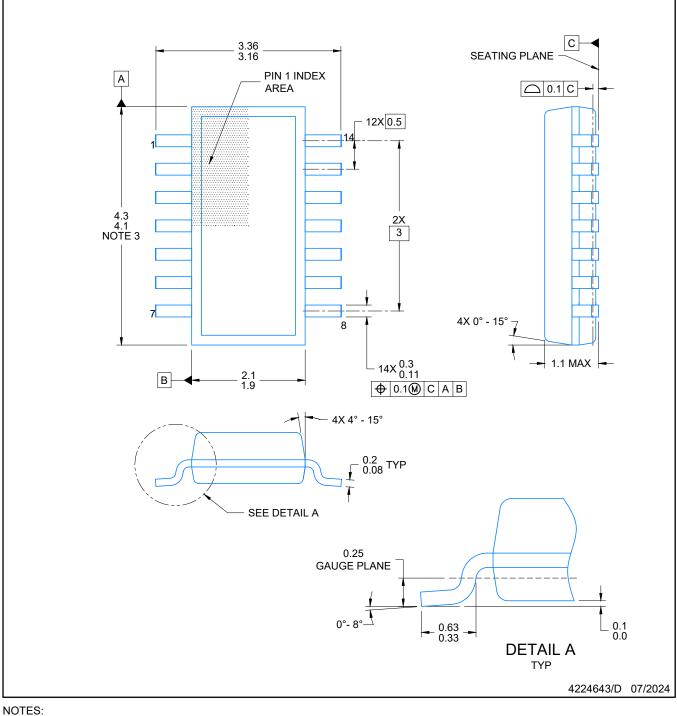




PACKAGE OUTLINE

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



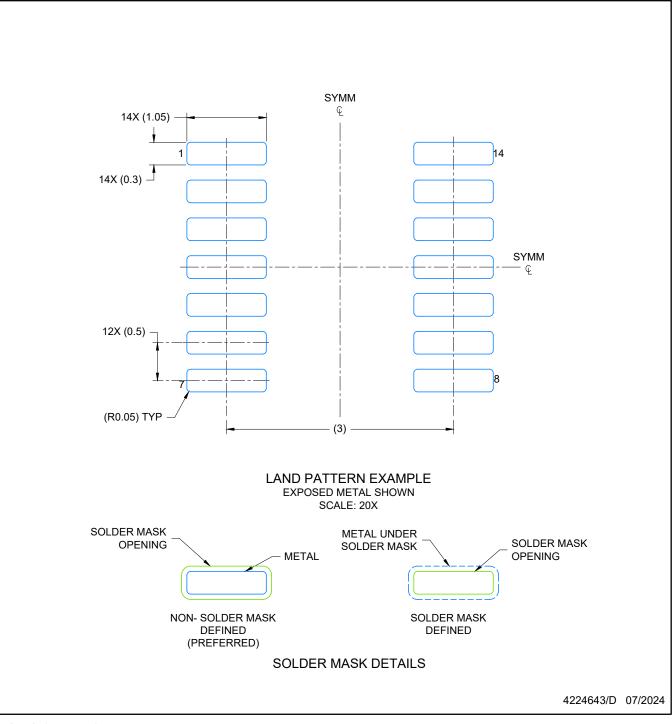
- IOTES.
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- 5. Reference JEDEC Registration MO-345, Variation AB



EXAMPLE BOARD LAYOUT

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

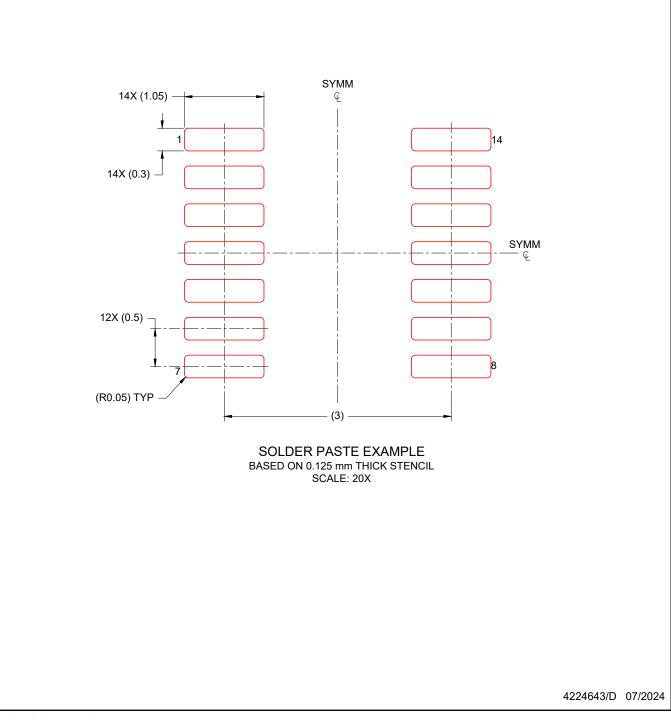
- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



EXAMPLE STENCIL DESIGN

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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